

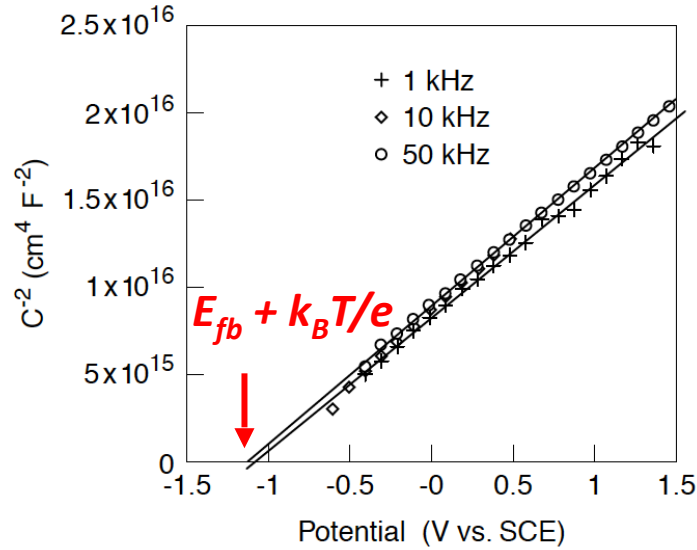
Energy Conversion by Semiconductor Devices

Jun-Ho YUM

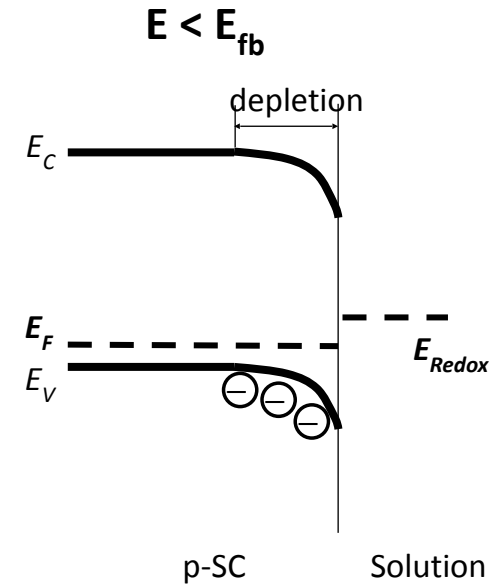
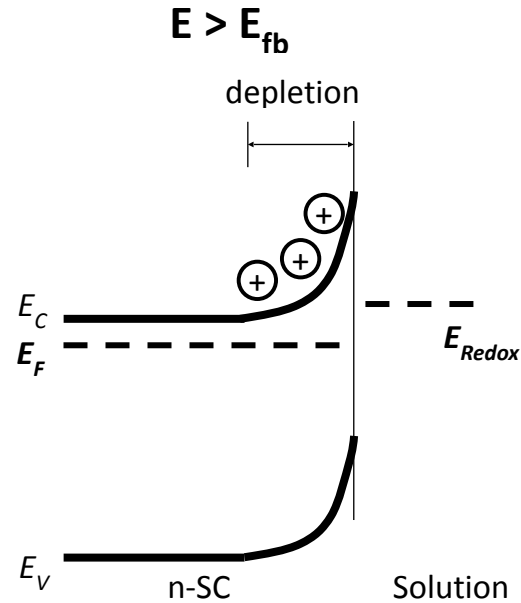
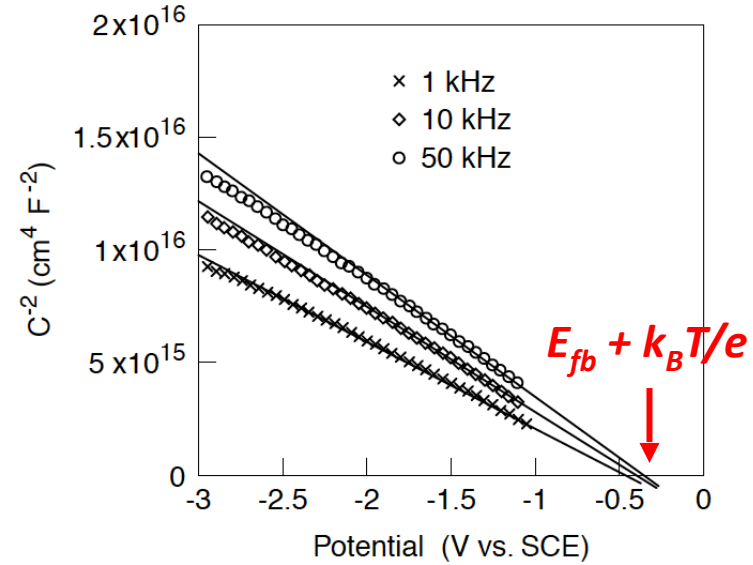
junho.yum@epfl.ch

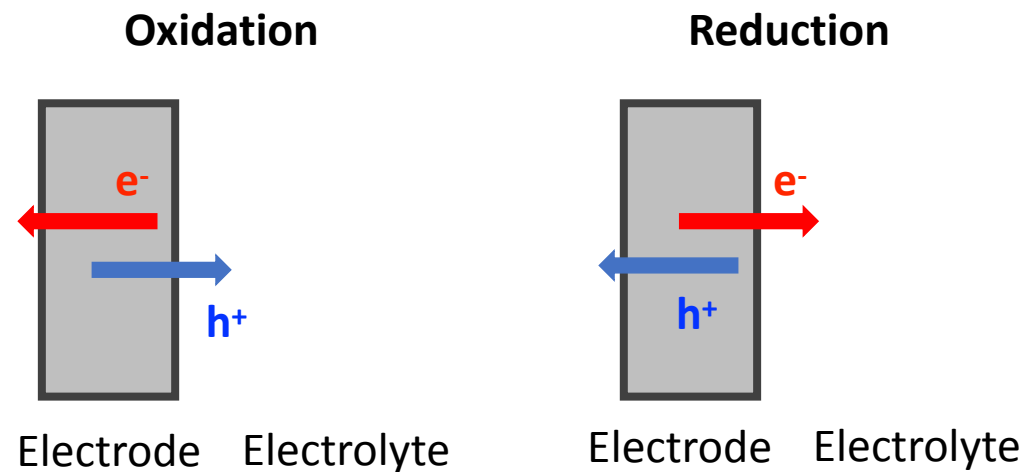
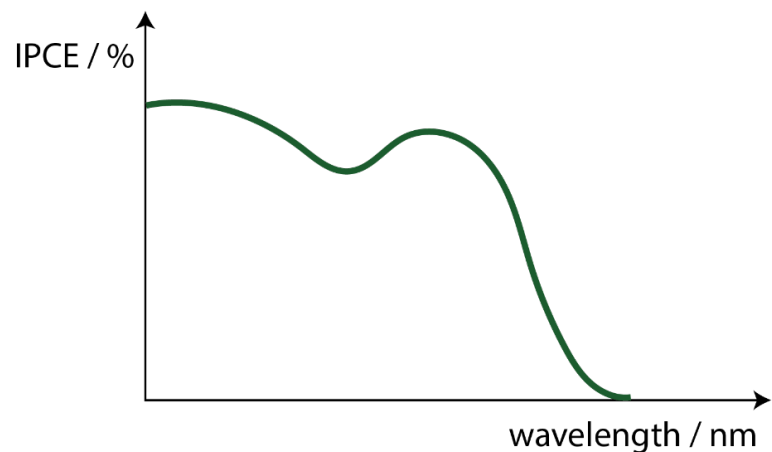
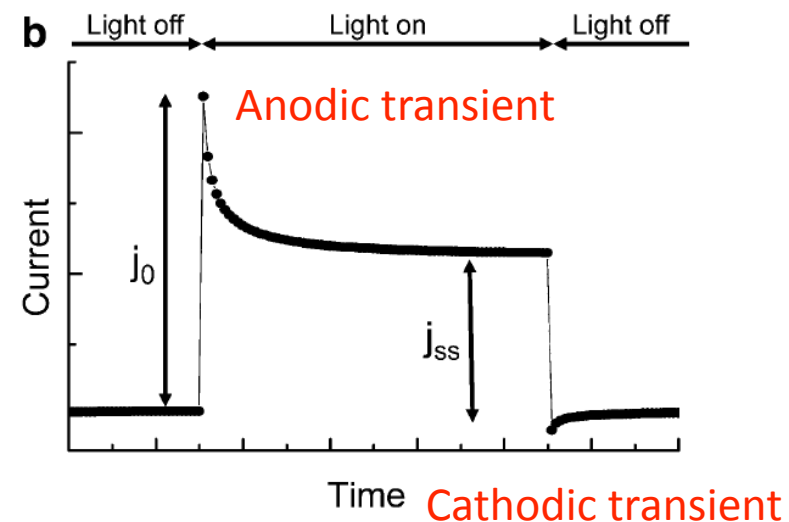
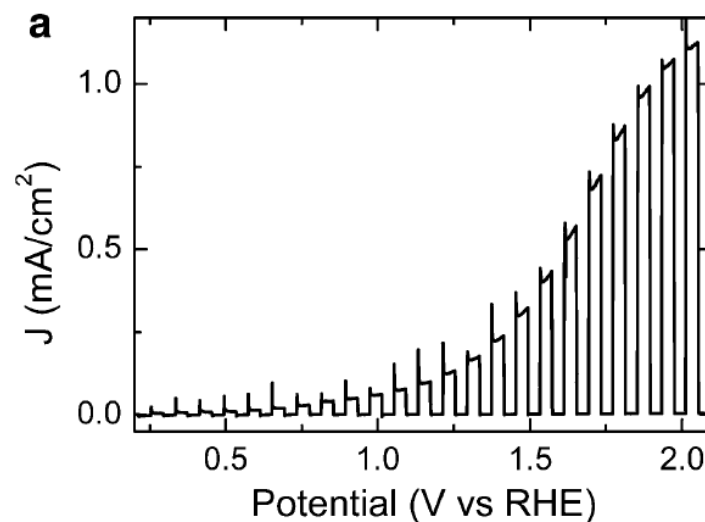
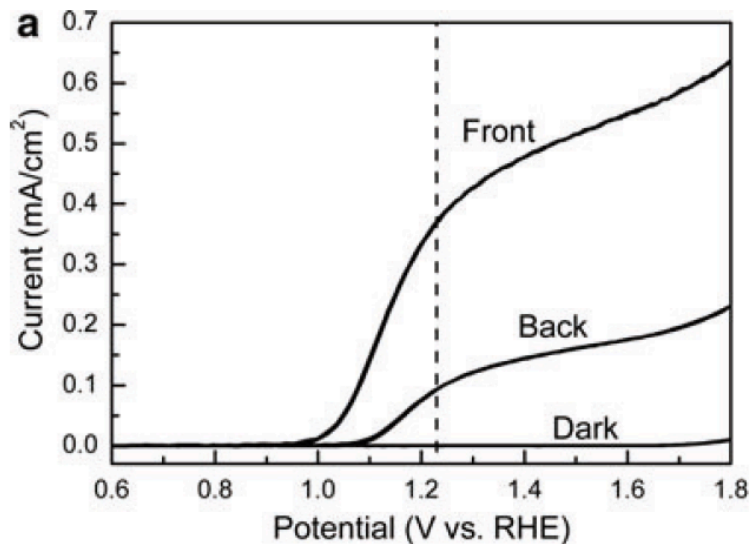
Recap: Mott-Schottky Equation

MS plot for an n-type silicon



MS plot for an p-type silicon





- Solar-To-Hydrogen (STH) efficiency is defined as ***chemical energy of the hydrogen produced*** divided by ***solar energy input from sunlight incident on the process***.
- The ***chemical energy of the hydrogen produced*** = The rate of hydrogen production (mmol H₂/s) multiplied by the change in Gibbs free energy per mole of H₂ ($\Delta G^0 = 237.2$ kJ/mol at 25 °C).

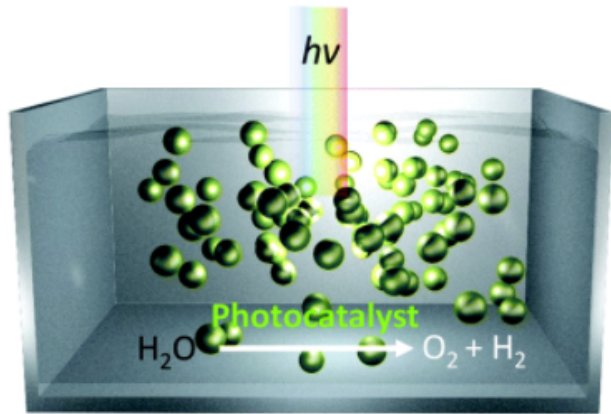
$$STH = \left[\frac{(\text{mmol H}_2/\text{s}) \times (237,200 \text{ J/mol})}{P_{total} \left(\frac{\text{mW}}{\text{cm}^2}\right) \times \text{Area} (\text{cm}^2)} \right]_{AM1.5G}$$

← This equation calculates the power output (numerator) based on the direct measurement of the true H₂ production rate by an analytical method such as gas chromatography or mass spectrometry.

$$STH = \left[\frac{(J_{sc} (\text{mA/cm}^2)) \times (1.23 \text{ V}) \times \eta_F}{P_{total} \left(\frac{\text{mW}}{\text{cm}^2}\right)} \right]_{AM1.5G}$$

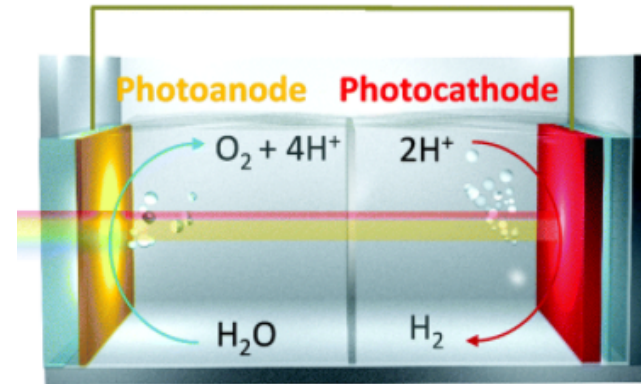
← Alternatively, this equation uses the relation that power is the product of the minimum energy to split water, current, and the Faradaic efficiency for hydrogen evolution

PC



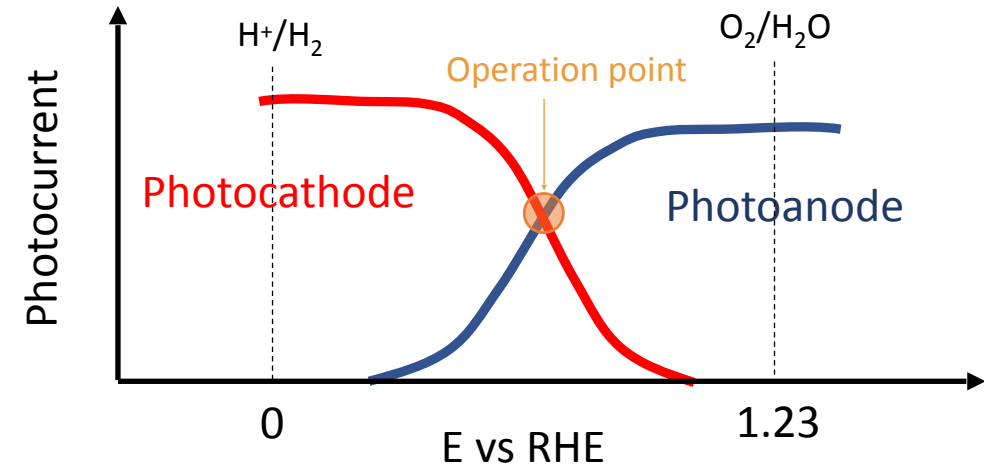
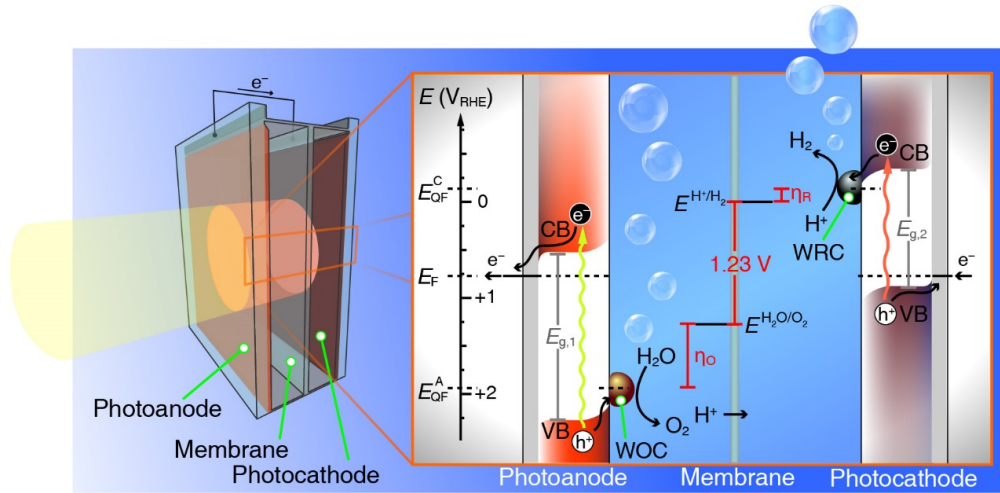
$$STH = \left[\frac{(\text{mmol } H_2/\text{s}) \times (237,200 \text{ J/mol})}{P_{total} \left(\frac{\text{mW}}{\text{cm}^2}\right) \times \text{Area} (\text{cm}^2)} \right]_{AM1.5G}$$

PEC



$$STH = \left[\frac{(J_{sc} (\text{mA}/\text{cm}^2) \times (1.23 \text{ V}) \times \eta_F)}{P_{total} \left(\frac{\text{mW}}{\text{cm}^2}\right)} \right]_{AM1.5G}$$

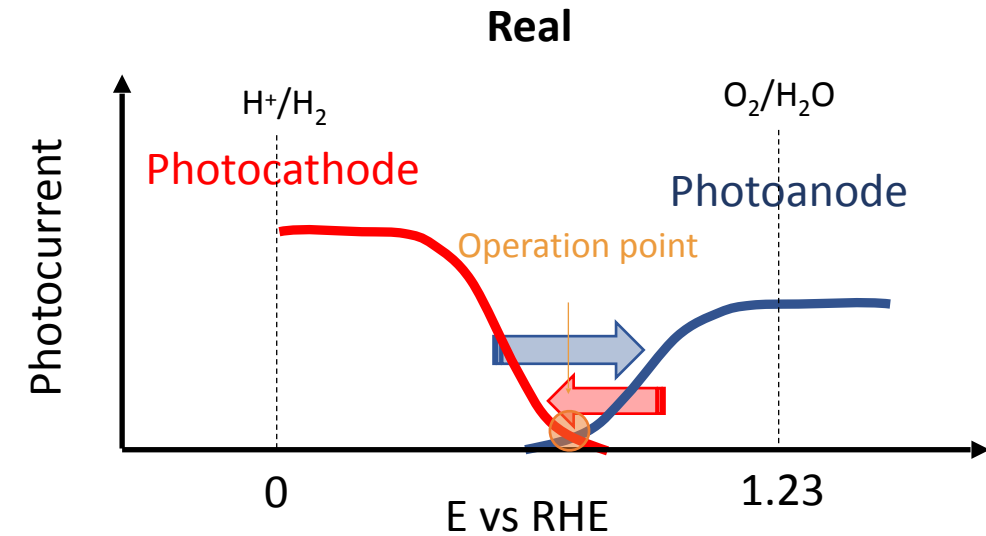
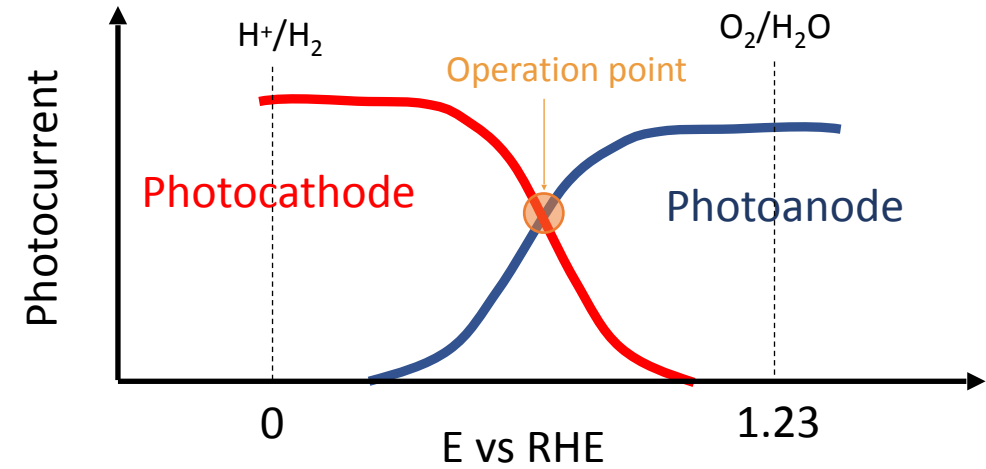
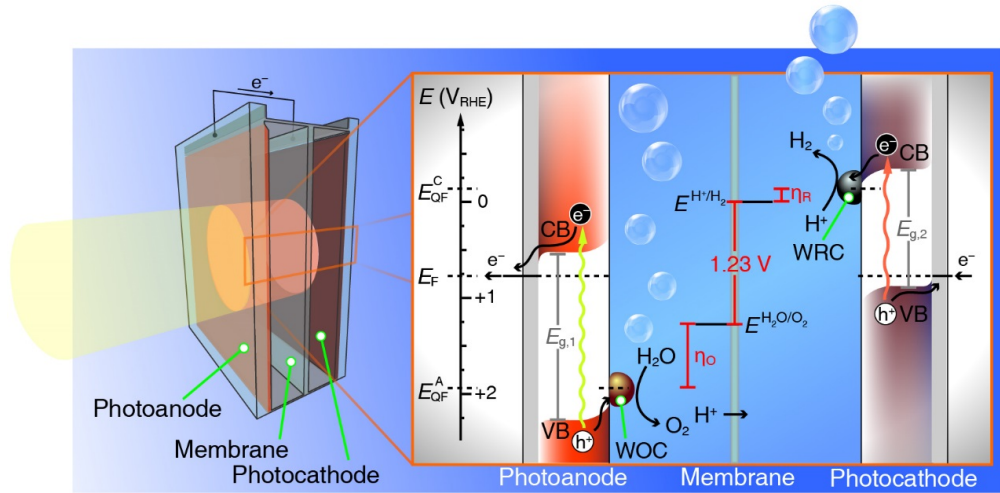
Assessment of a Dual Tandem PEC Cell



Examine separately photoelectrodes.

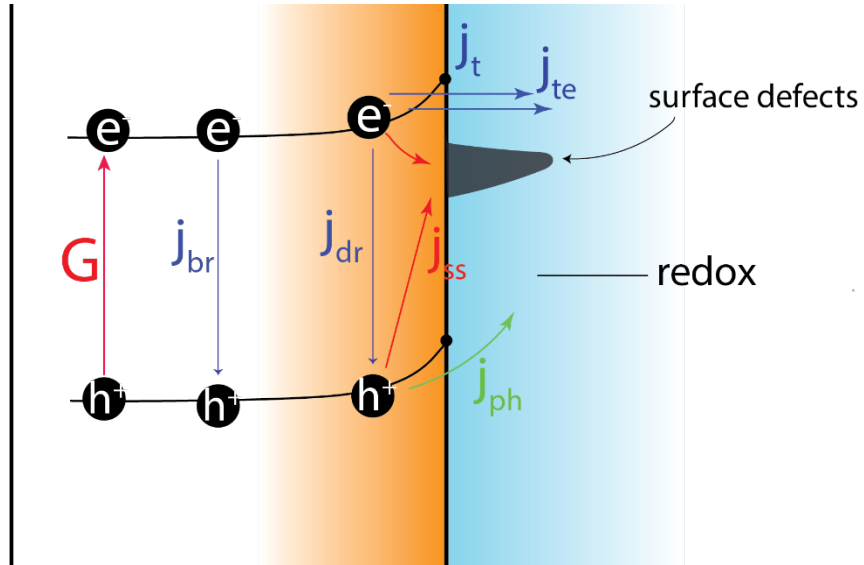
Predict 'best' performance (*overlapping of JV curves*)

Assessment of a Dual Tandem PEC Cell



Today's low-cost PEC cells suffer from poor STH

- Poor performance of photoelectrodes
- Non-optimized combination of photoelectrodes (band gaps)



$$J_{ph} = G - J_{br} - J_{dr} - J_{ss} - J_t - J_{te}$$

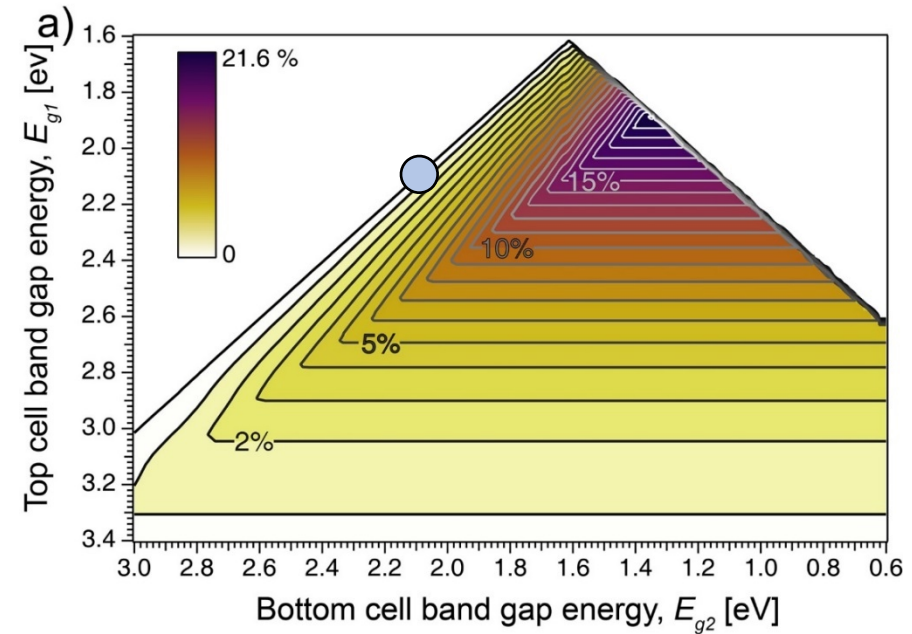
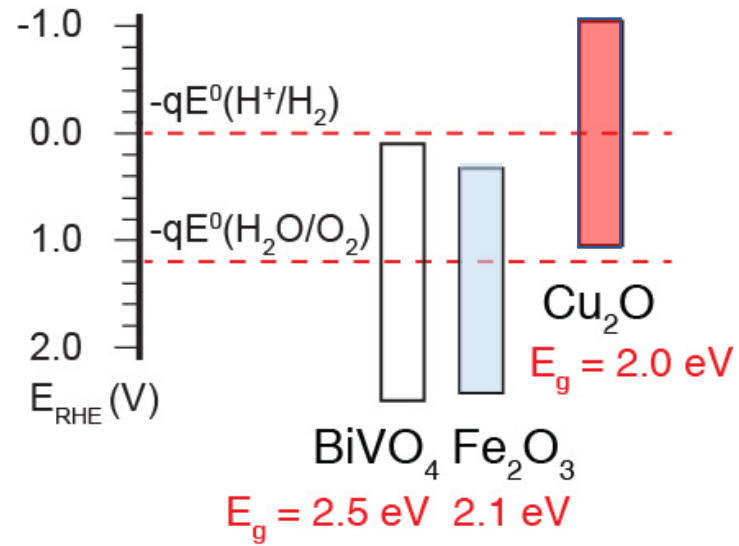
- Charge recombination in the bulk (br), in the depletion layer (dr) and via surface states (ss).
- Electron losses by reaction with redox through tunneling (t) across the potential barrier or at the surface (te)

BULK PROPERTIES

- Bulk defects (recombination)
- Carrier transport
- Doping density (conductivity, depletion depth)
- Morphology (charge collection)

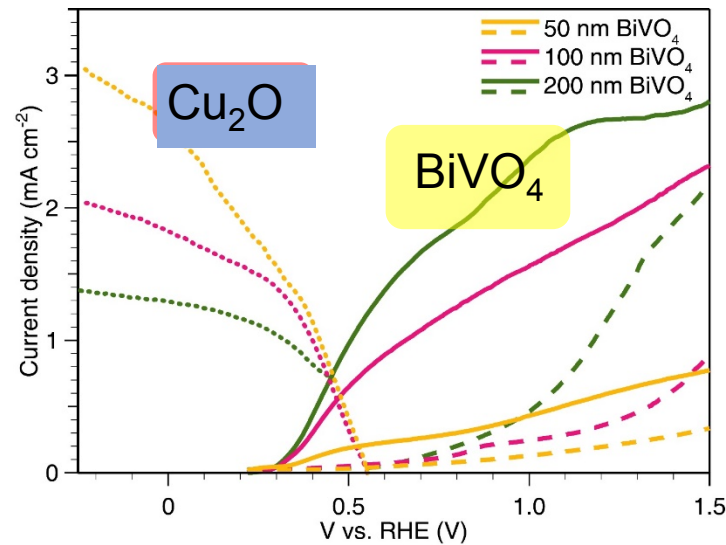
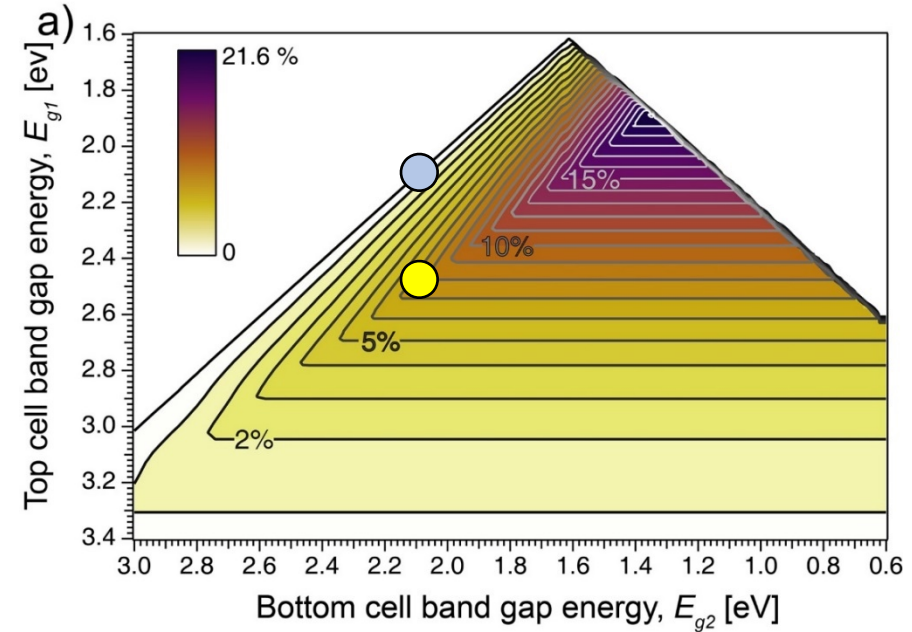
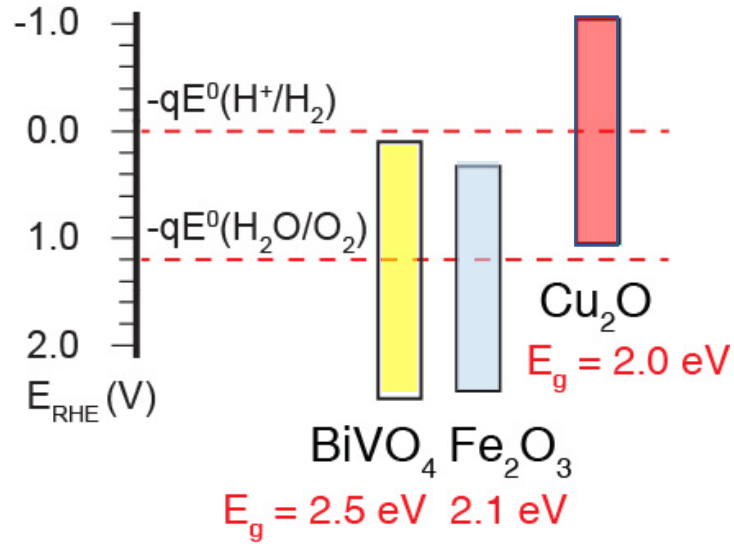
SURFACE PROPERTIES (Semiconductor-liquid junction)

- Surface defects (recombination)
- Catalytic properties
- Stability



Low performance (non-complementary light absorption).
Hematite filters useful light for Cu_2O

Assessment of a Dual Tandem PEC Cell

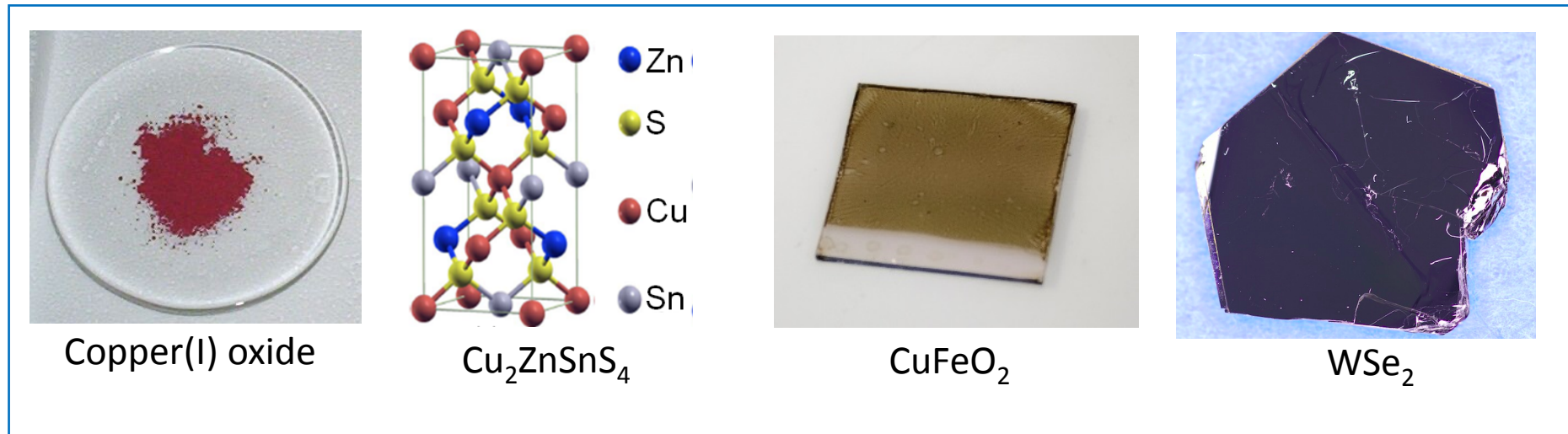


Optimized combination of photoelectrodes (band gaps and thickness) are needed!

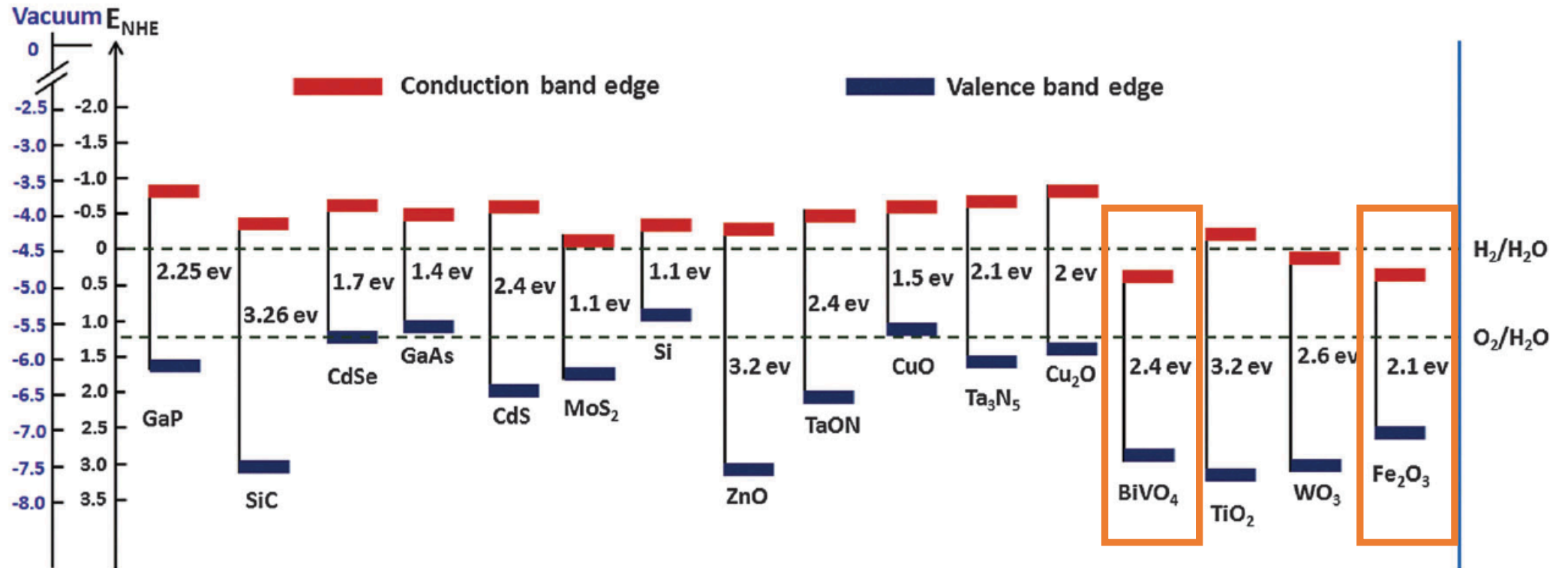
Photoanode (n-type SC)



Photocathode (p-type SC)



Band edge positions of semiconductors in contact with the aqueous electrolyte at pH = 0 relative to NHE and the vacuum level.



Advantages

- Cheap and abundant (Fe in the earth crust, 5.6% by weight)
- Stable
- Environmentally benign
- Absorbs over 16 % (AM 1.5G, $E_g = 2.1$ eV)
- Theoretical max STH = 15%, $J_{max} = 12.5$ mA/cm²

Challenges

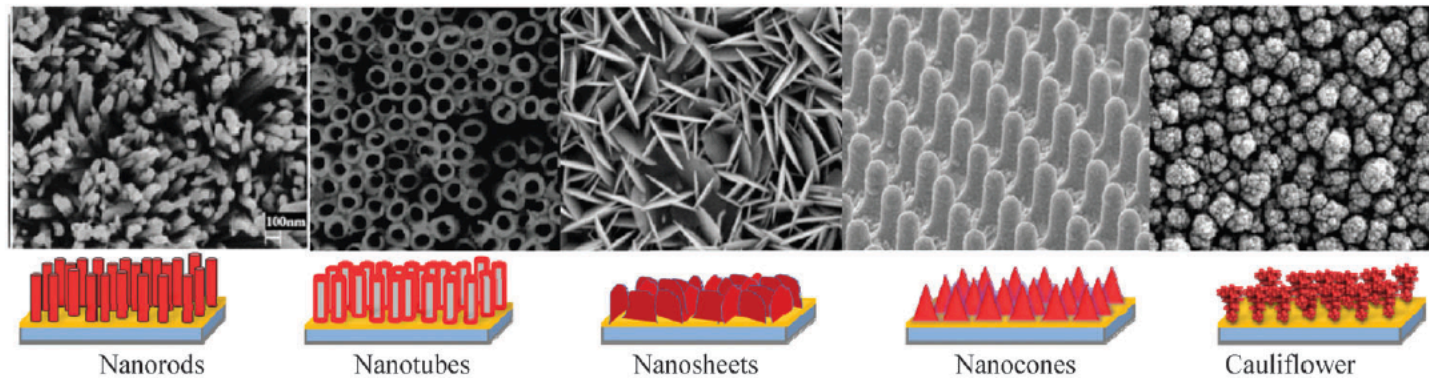
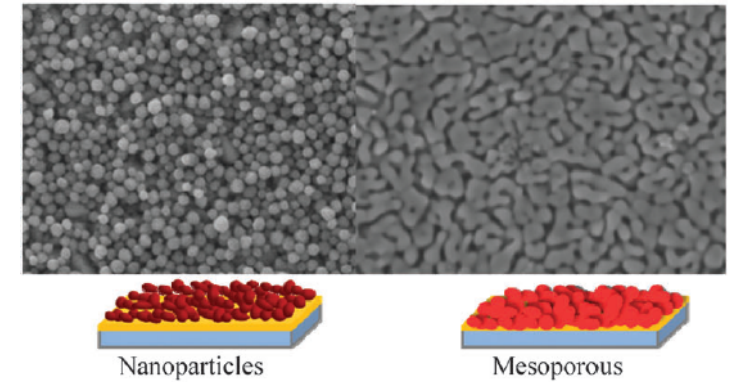
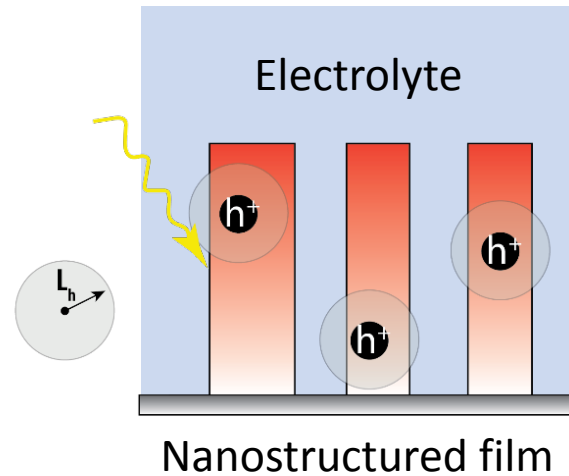
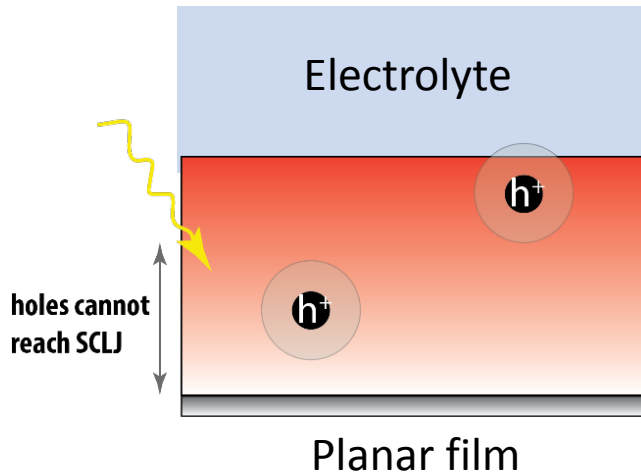
Bulk problems

- Short hole diffusion length ($L_D = 5$ nm) (light penetration depth of 118 nm at 550 nm wavelength)
- Poor conductivity (10^{-6} $\Omega^{-1}\text{cm}^{-1}$ for single crystal and 10^{-14} $\Omega^{-1}\text{cm}^{-1}$ for polycrystal)

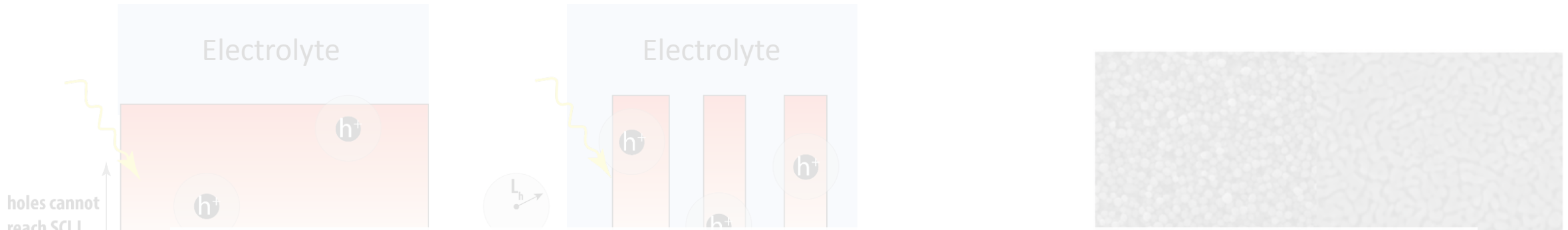
Surface problems

- High overpotential for water oxidation kinetics (surface trap states)

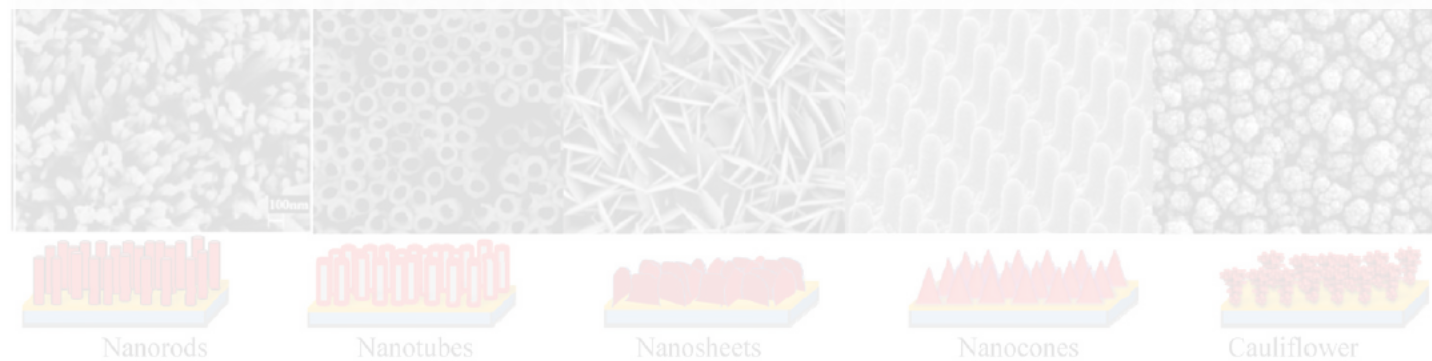




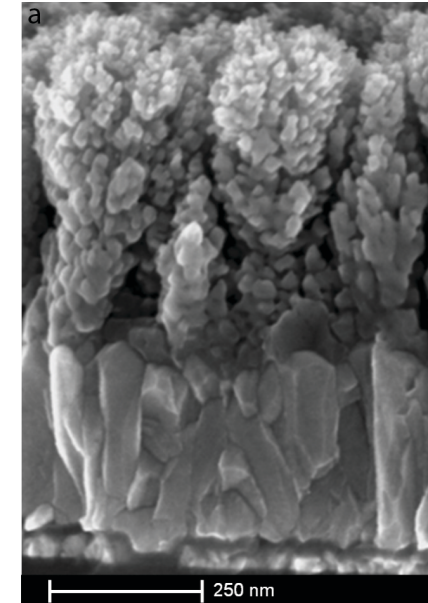
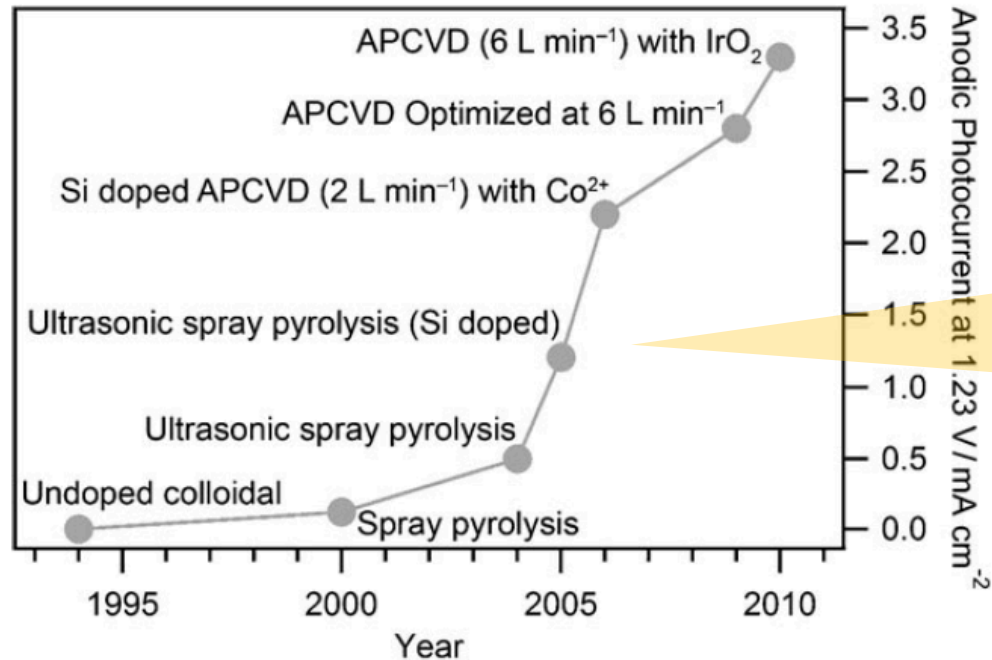
A. G. Tamirat et al., *Nanoscale Horiz.*, **1**, 243 (2016)



A nanostructure's large aspect ratio provides a long optical path for improved light absorption along the vertical axis, while its much smaller diameter facilitates collection of minority carriers over a shorter distance, minimizing the probability of recombination within the absorber material.



A. G. Tamirat et al., *Nanoscale Horiz.*, 1, 243 (2016)

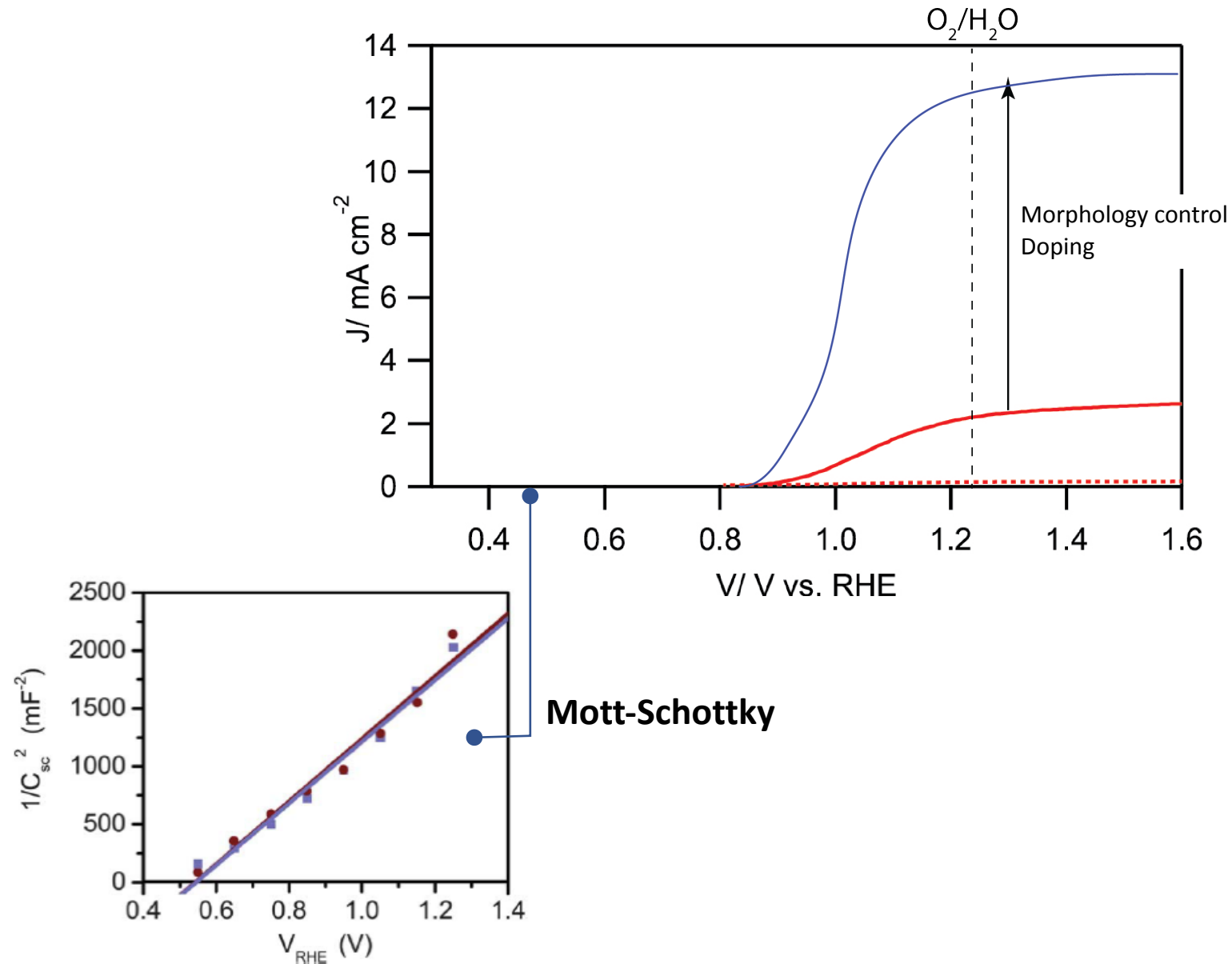
Si-doped
 Fe_2O_3 Substrate
(F:SnO₂)

K. Sivula et al., *Chemsuschem*, **4**, 432 – 449 (2011)

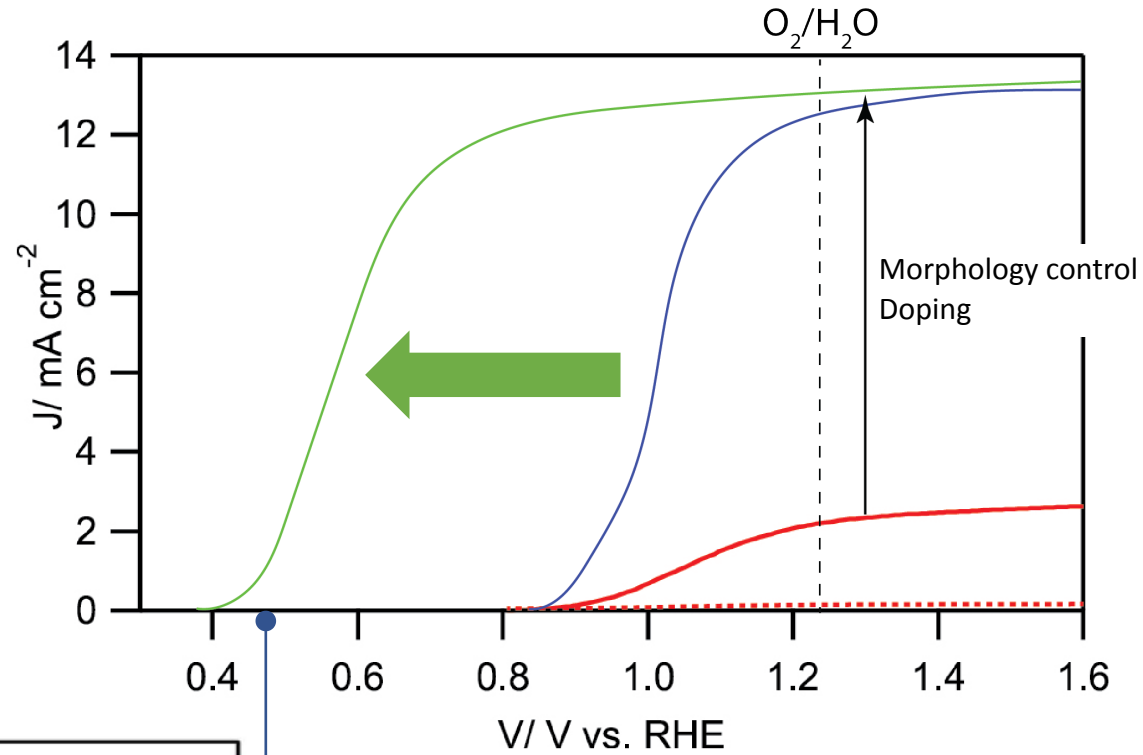
- Si^{4+} , Ti^{4+} , Sn^{4+} , Zr^{4+} , Nb^{5+} (n-type)
- Mg^{2+} , Cu^{2+} (p-type)

To promote charge transfer by increasing donor density and improve the electronic conductivity of hematite.

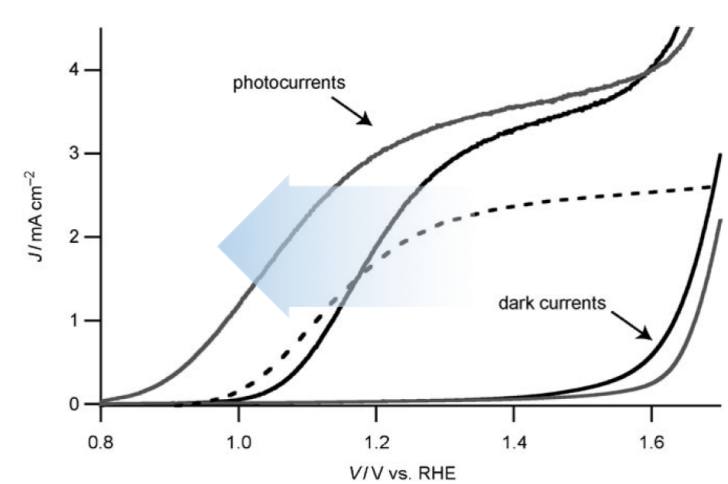
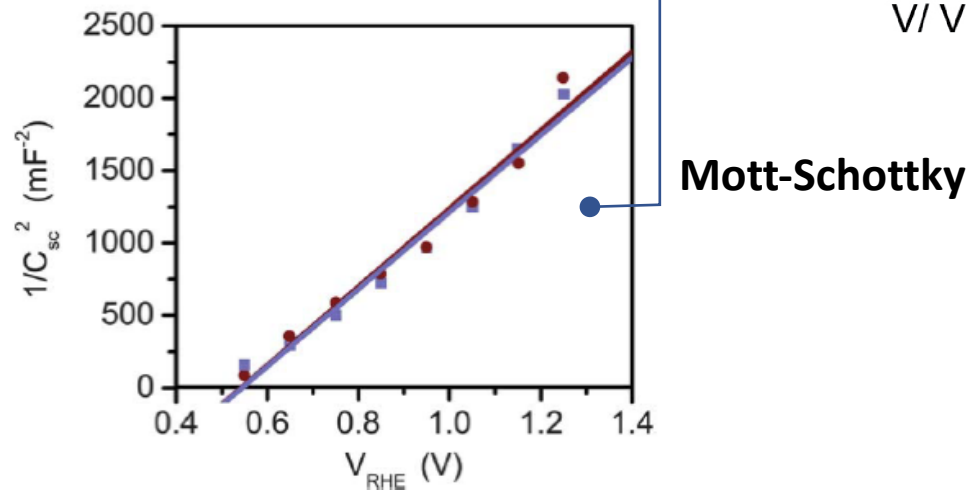
Ex) Zr^{4+} doped hematite: $0.1 \Omega^{-1}\text{cm}^{-1}$ with 10^{19}cm^{-3} doping concentration vs $10^{-14} \Omega^{-1}\text{cm}^{-1}$ for polycrystal



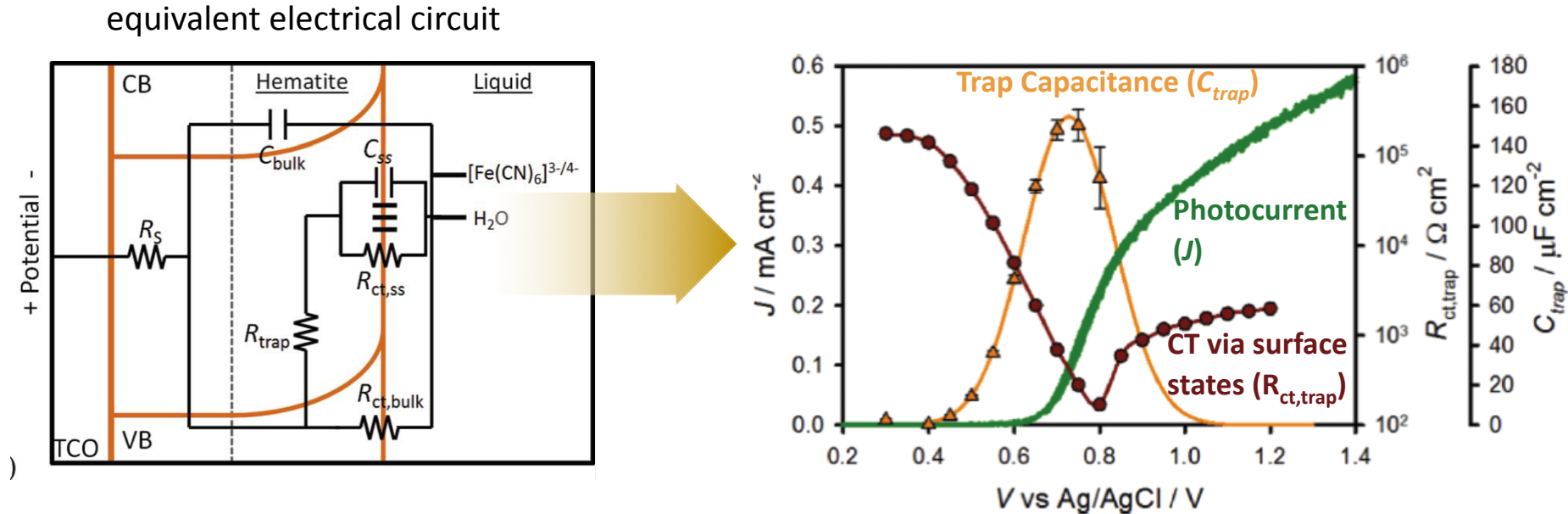
Overpotential Problems in $\alpha\text{-Fe}_2\text{O}_3$ (hematite)



Including IrO_2 catalyst shifts slightly the V_{ON} , but still far from V_{fb}



Surface recombination. Examining the electrochemical properties of the SCLJ

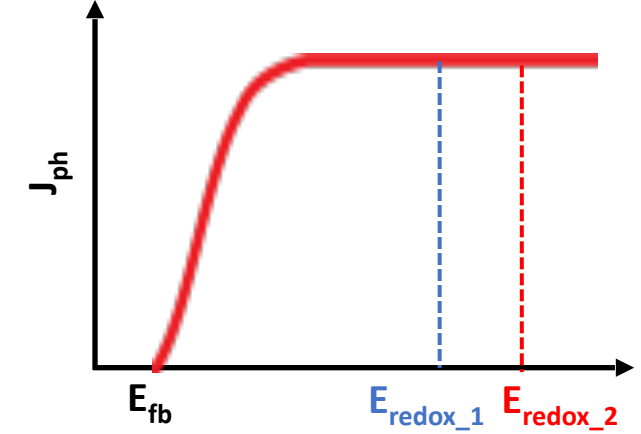
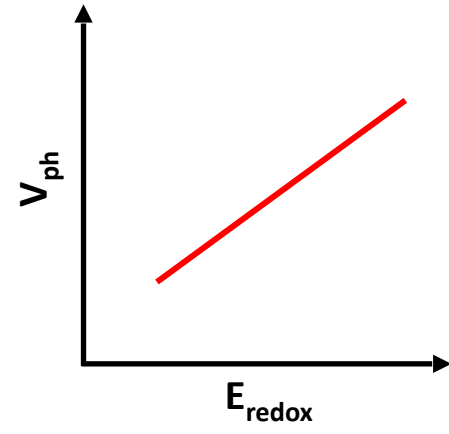
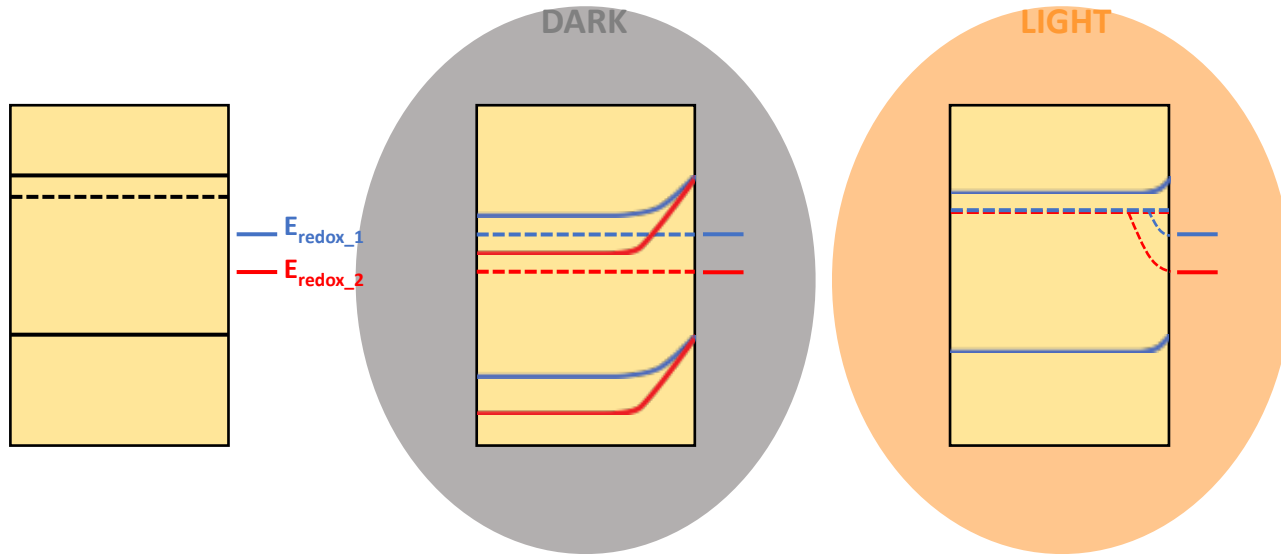


B. Klahr *et al.* *J. Am. Chem. Soc.*, **134**, 4294 (2012)

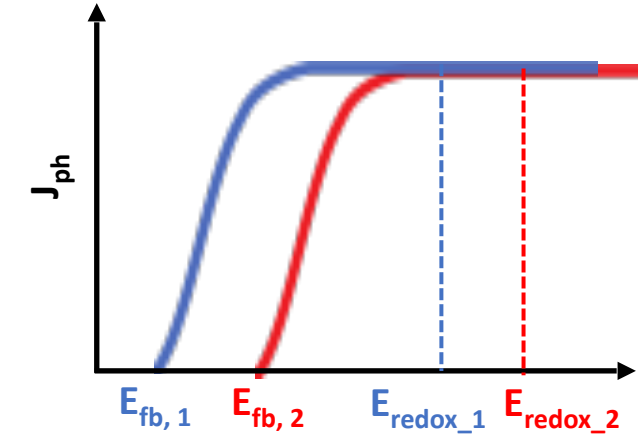
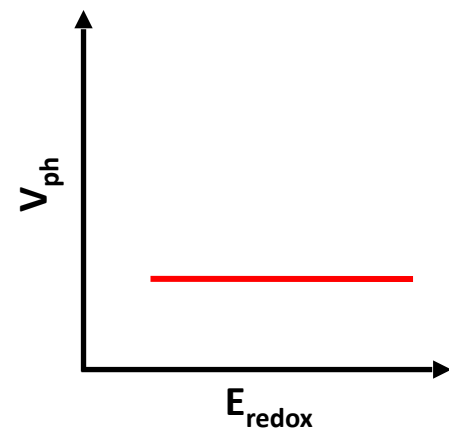
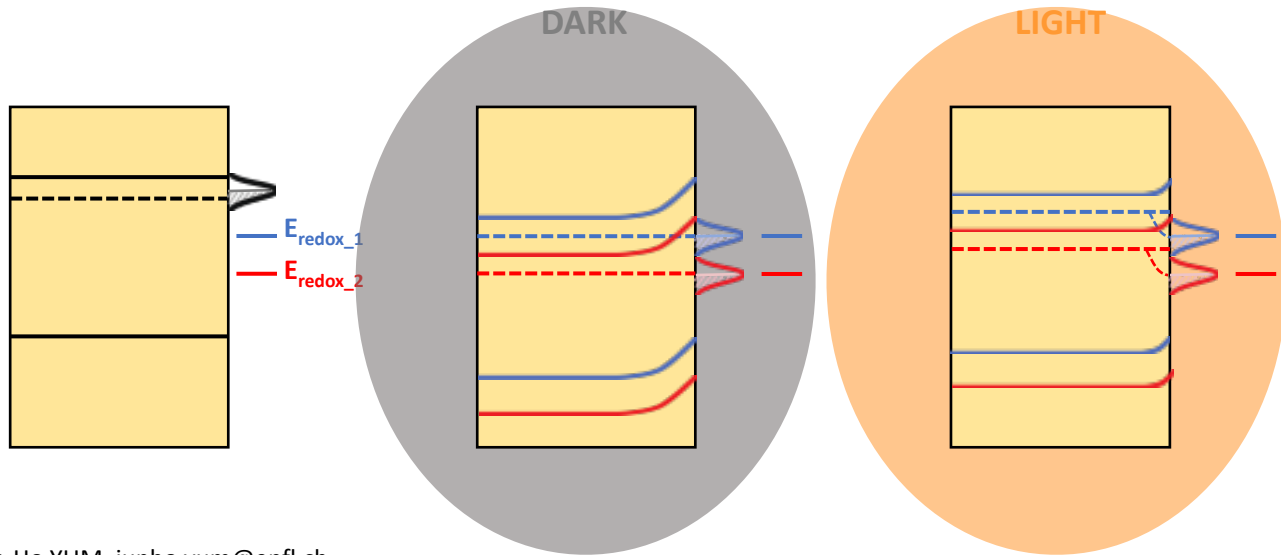
- C_{trap} indicate the **accumulation of charges at the SCLJ** just before the water oxidation starts.
- Charge transfer takes place from this surface state.
- Trapped charge carriers “pin” the Fermi level, **Fermi Level Pinning**, leading to **reduced band bending** and **delayed onset of photocurrent** (overpotential).

EPFL Fermi Level Pinning (FLP)

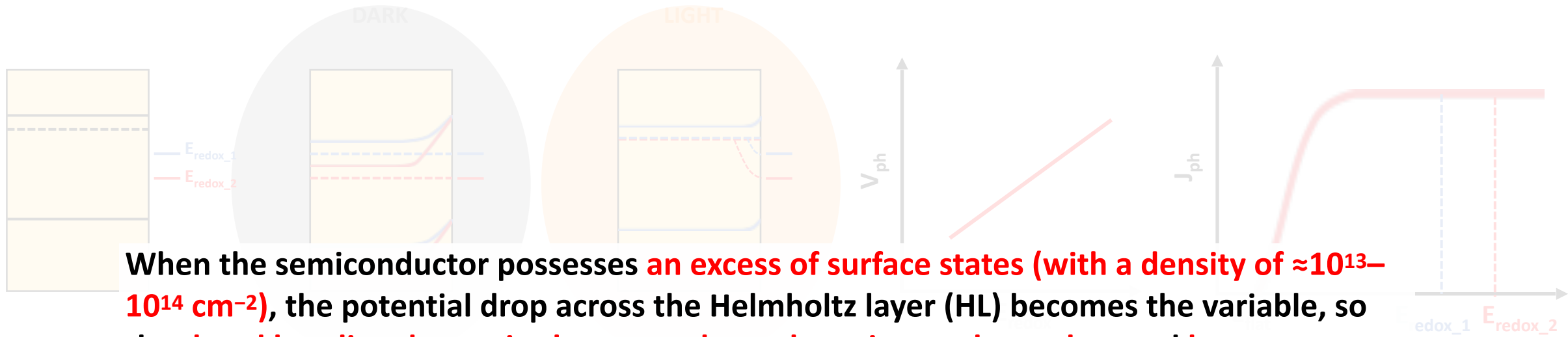
No surface state / No FLP (band edge pinning)



Presence of surface state/ Fermi Level Pinning

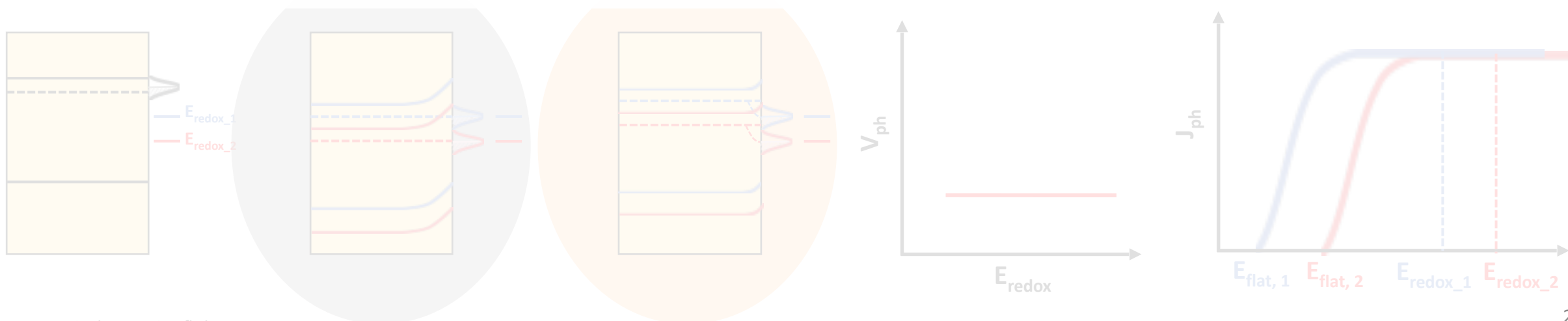


No surface state / No FLP (band edge pinning)



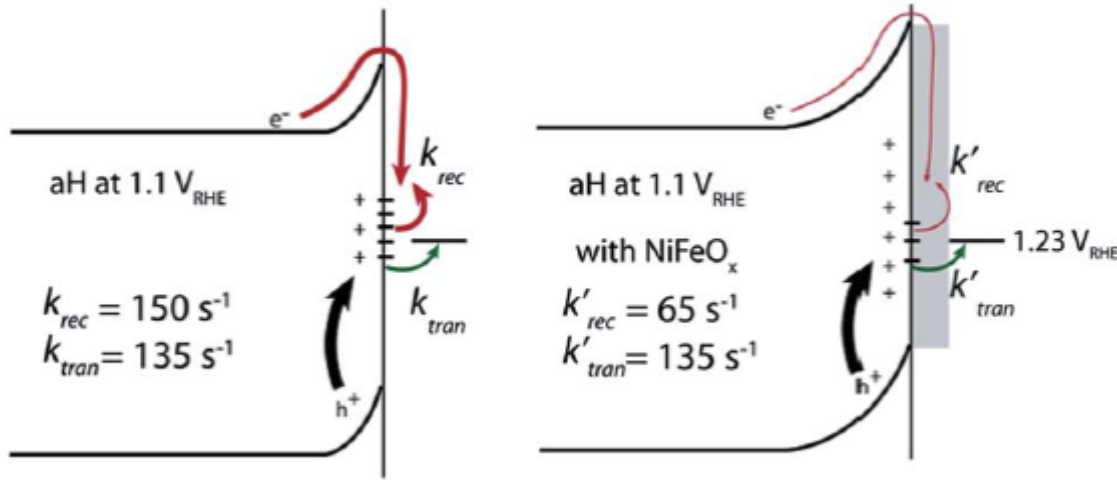
When the semiconductor possesses **an excess of surface states (with a density of $\approx 10^{13}$ – 10^{14} cm^{-2})**, the potential drop across the Helmholtz layer (HL) becomes the variable, so that **band bending degree in the space charge layer is greatly weakened and becomes independent of the applied bias**. This effect is called **Fermi-level pinning**.

Under Fermi-level pinning conditions, the degree of band bending remains unchanged.

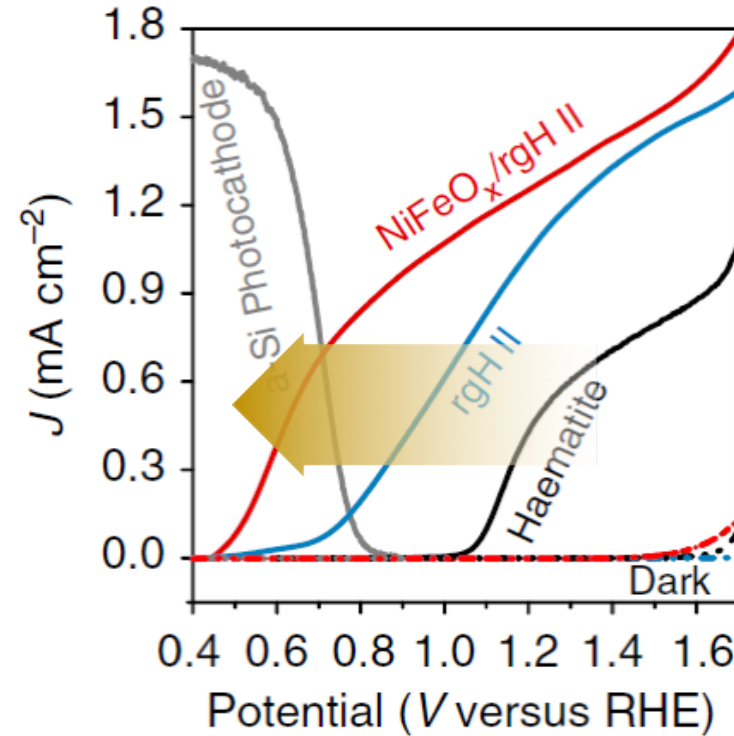


Surface Problems in $\alpha\text{-Fe}_2\text{O}_3$ (hematite) – Overpotential

Surface recombination. Examining the electrochemical properties of the SCLJ



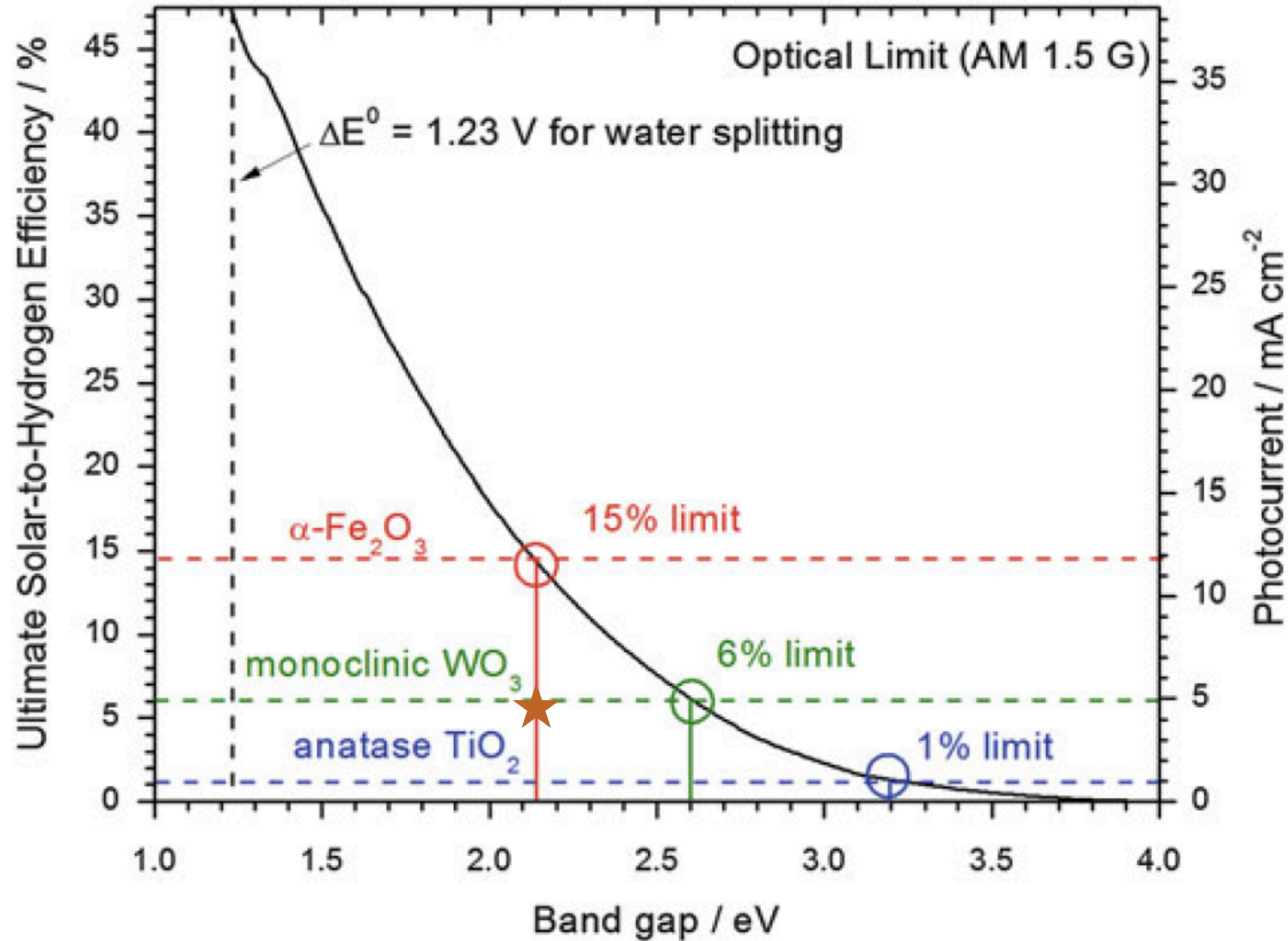
NiFeO_x passivate surface traps.



Deposition of NiFeO_x shifts V_{on} close to V_{fb} !!!

Thorne et al. *Chem. Sci.* **7**, 3347 (2016)

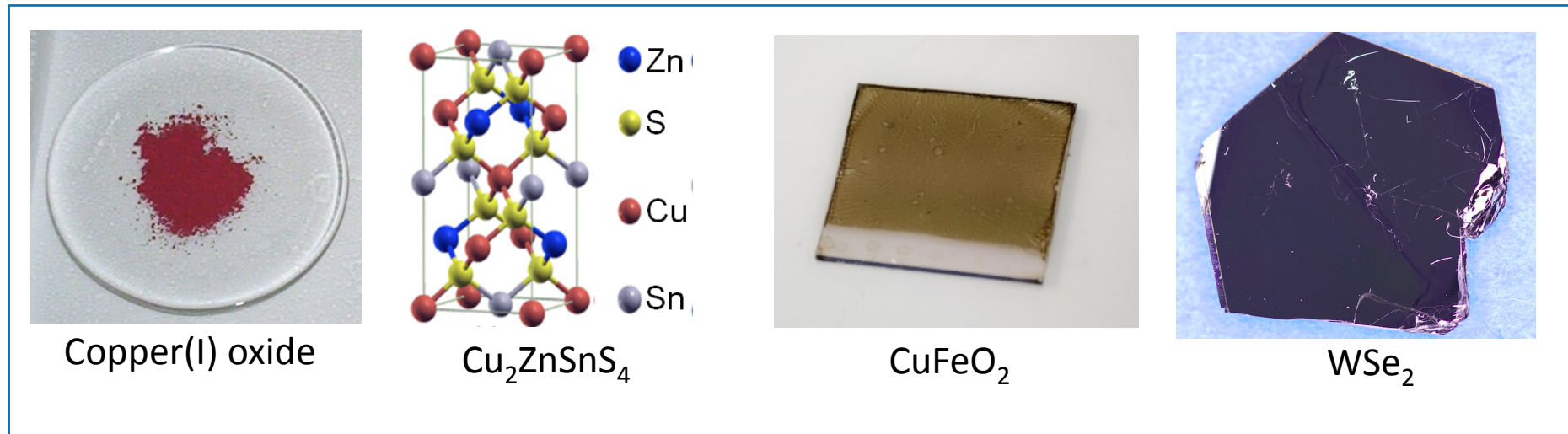
Jang et al. *Nature Commun.* **6**, 7447 (2015)

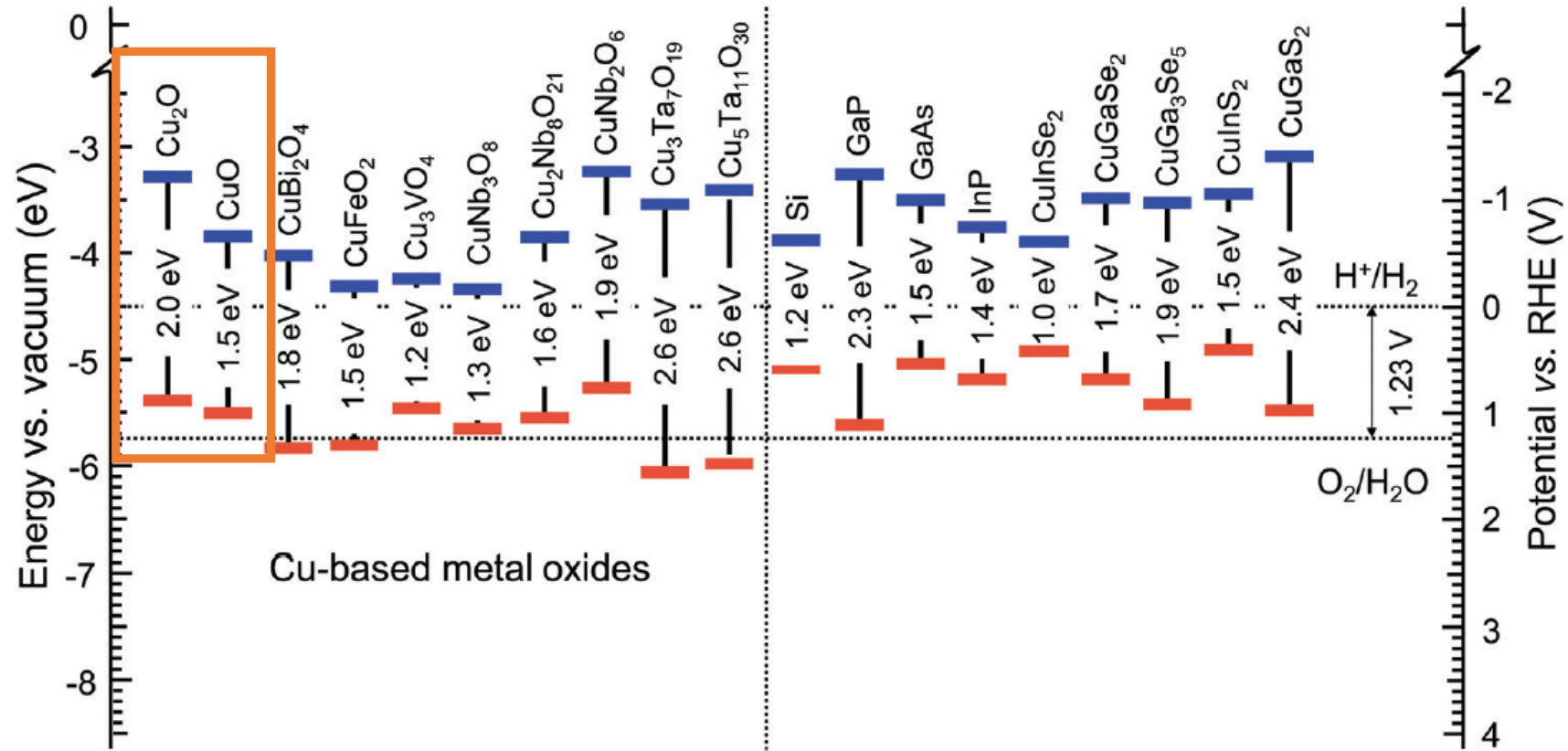


Photoanode (n-type SC)



Photocathode (p-type SC)





C. Li et al., *Energy Environ. Sci.*, **13**, 3269 – 3306 (2020)

Advantages

- Cheap and abundant
- Environmentally benign
- Band gap 2 eV



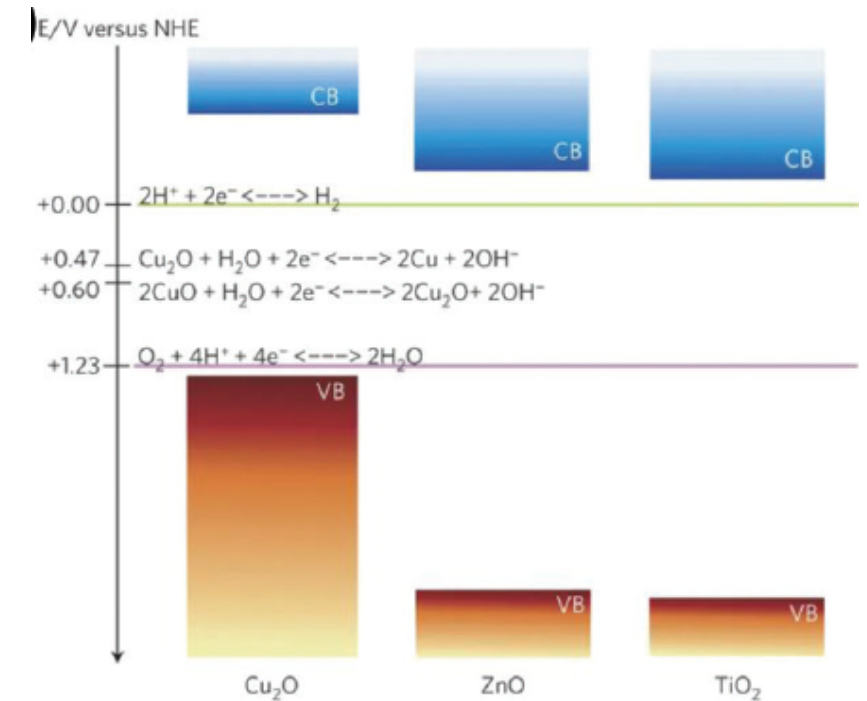
Challenges

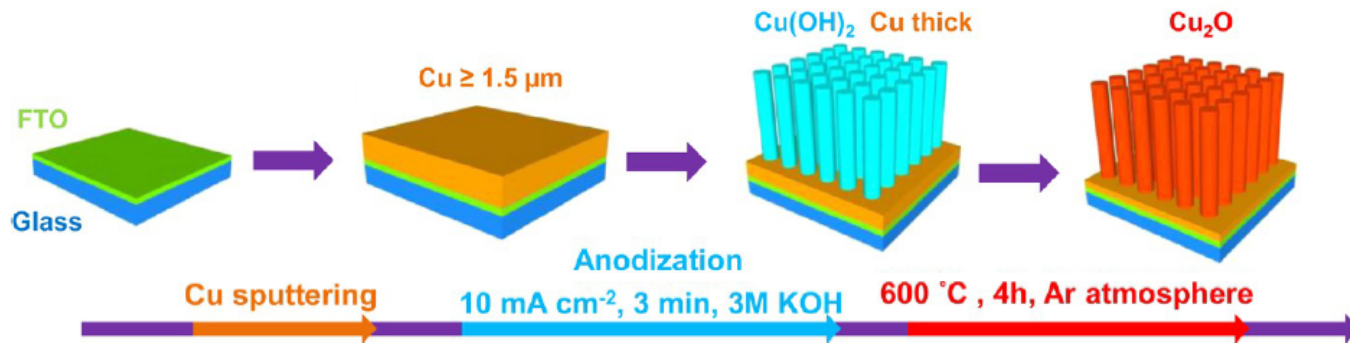
Bulk problems

- Minority carrier diffusion length around 200 nm (light penetration depth over 1 μm at 550 nm)

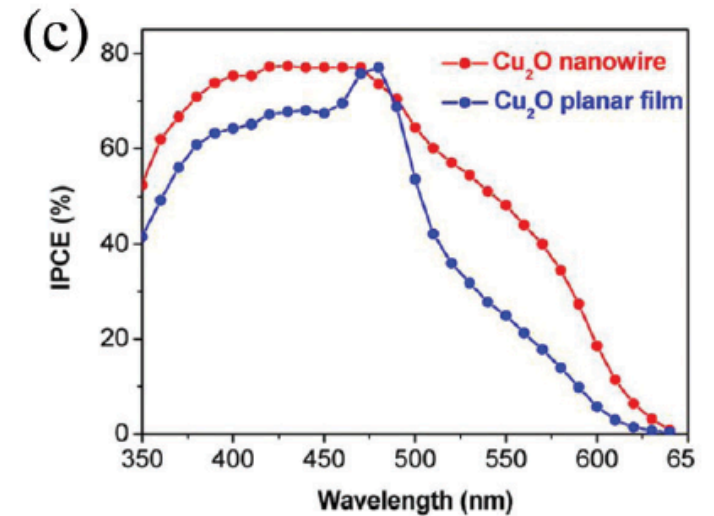
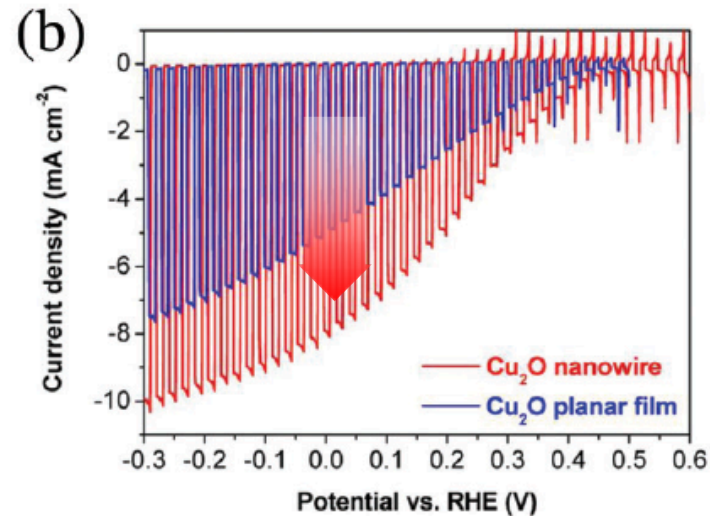
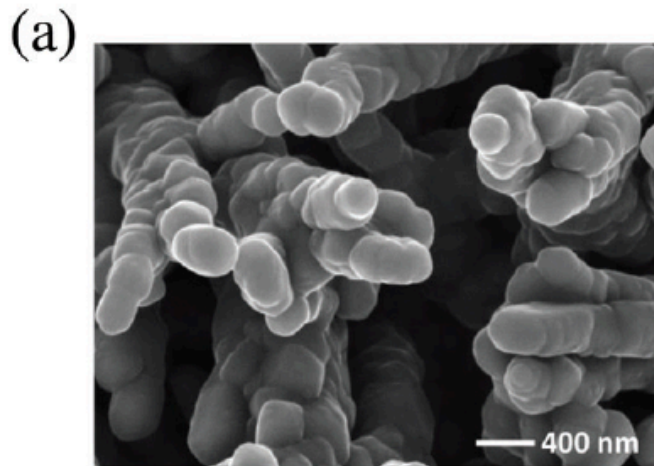
Surface problems

- Instability under operational condition (Facile reduction to Cu)



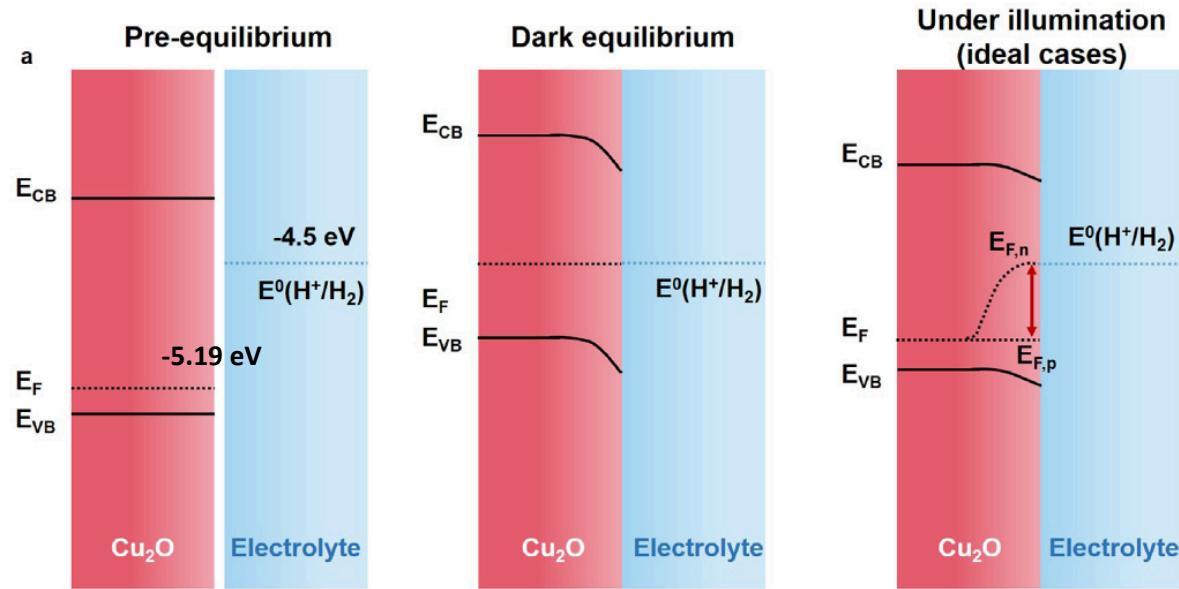
Photocathode: $\text{Cu}_2\text{O}/\text{AZO}/\text{TiO}_2/\text{RuO}_x$

- Nanowire Cu_2O
- 20 nm Al-doped ZnO/100nm TiO_2 forms a buried p-n junction
- RuO_x catalyst

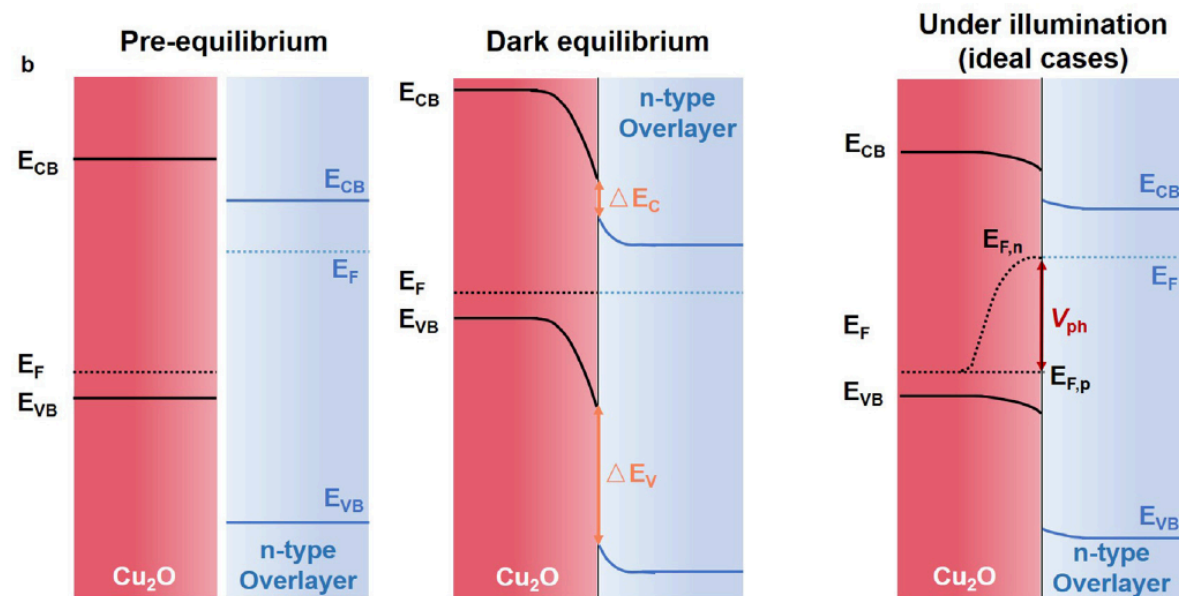


J. Luo et al., *Nano Lett.*, **16**, 1848 – 1857 (2016)

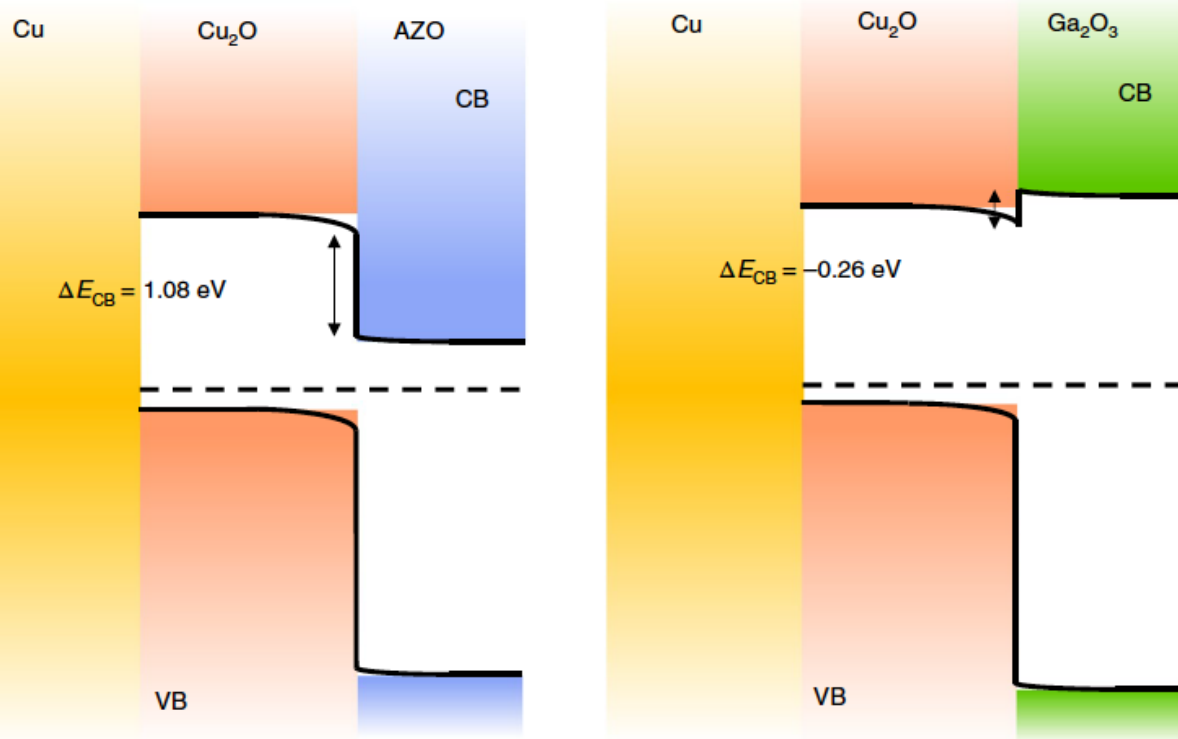
Cu_2O -liquid junction



Cu_2O -n-type overlayer heterojunction (called buried junction)

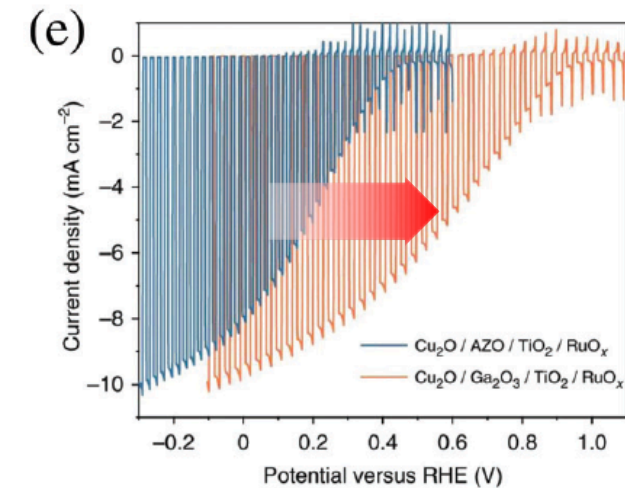
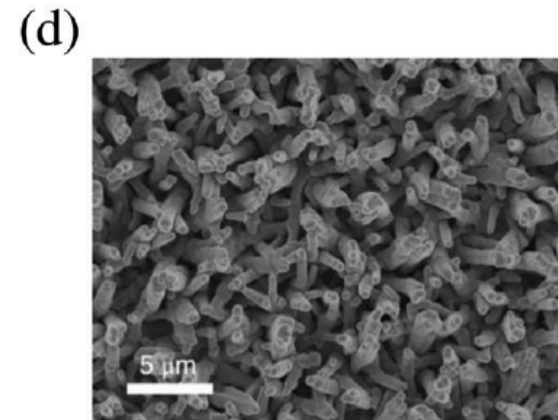


- Improved photovoltage
- Passivation against photocorrosion
- Still limited photovoltage due to a large conduction band offset



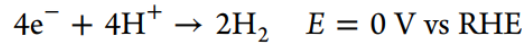
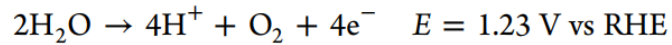
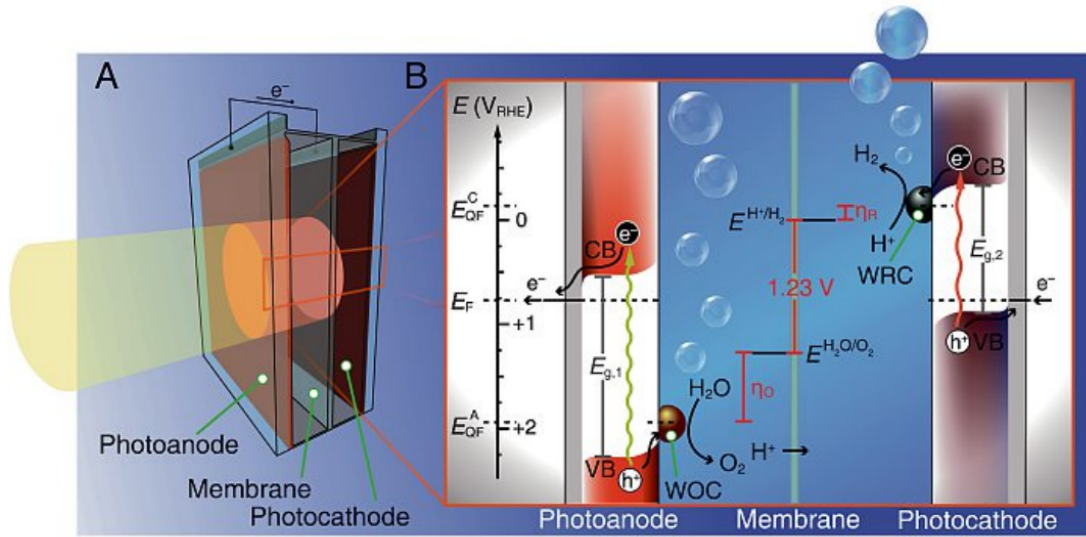
Photocathode: $\text{Cu}_2\text{O}/\text{Ga}_2\text{O}_3/\text{TiO}_2/\text{RuO}_x$

- The C.B offset between Cu_2O and Ga_2O_3 is small.
- A build-up of a large photovoltage.



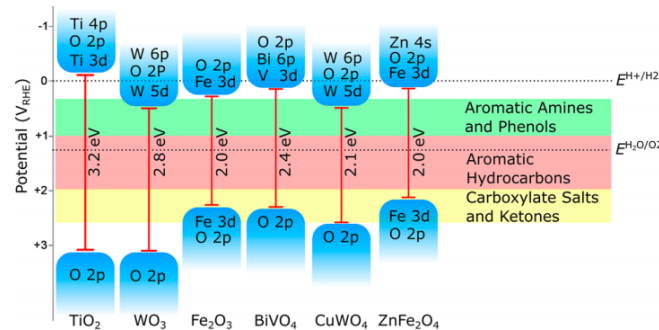
L. Pan et al., *Nature Catalysis*, **1**, 412 – 420 (2018)

- The formation of a **SEMICONDUCTOR-LIQUID JUNCTION (SCLJ)** can drive stand-alone photoelectrochemical reactions.
- There is still need for finding **NEW MATERIALS** for the design of tandem cells (complementary light absorption, robustness, excellent optoelectronic properties)
- Development of **NOVEL STRATEGIES** to effectively address issues like poor diffusion length, bulk recombination and/or surface recombination.



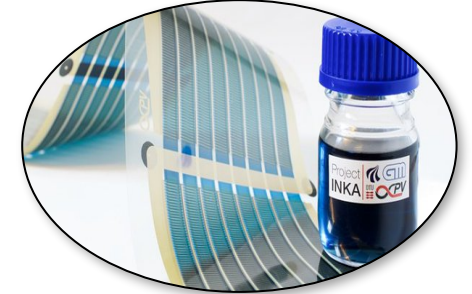
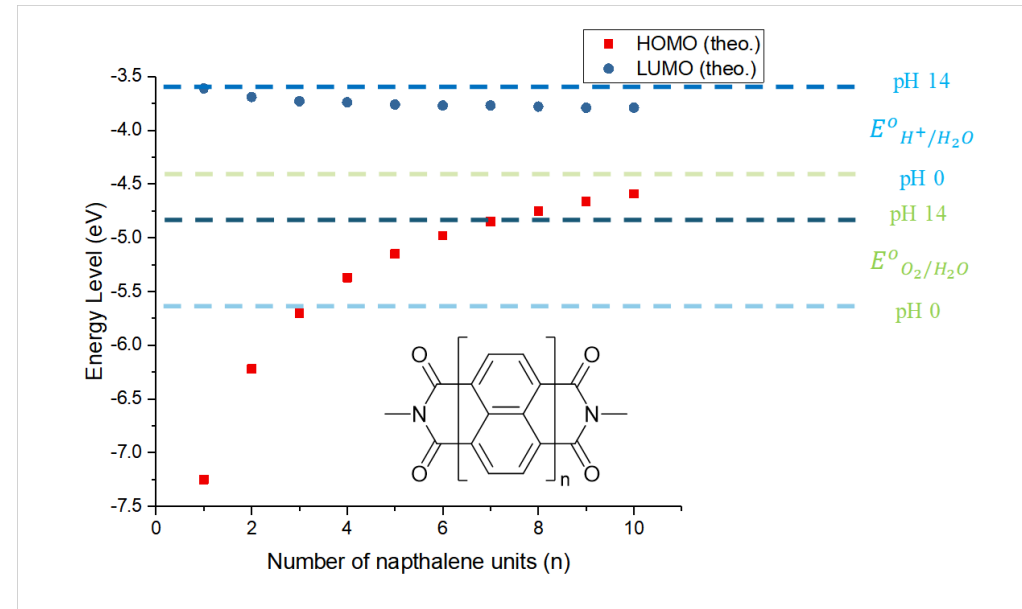
Inorganic semiconductors

- ✓ Harsh preparation condition
- ✓ Poor charge separation
- ✓ Fixed energy level

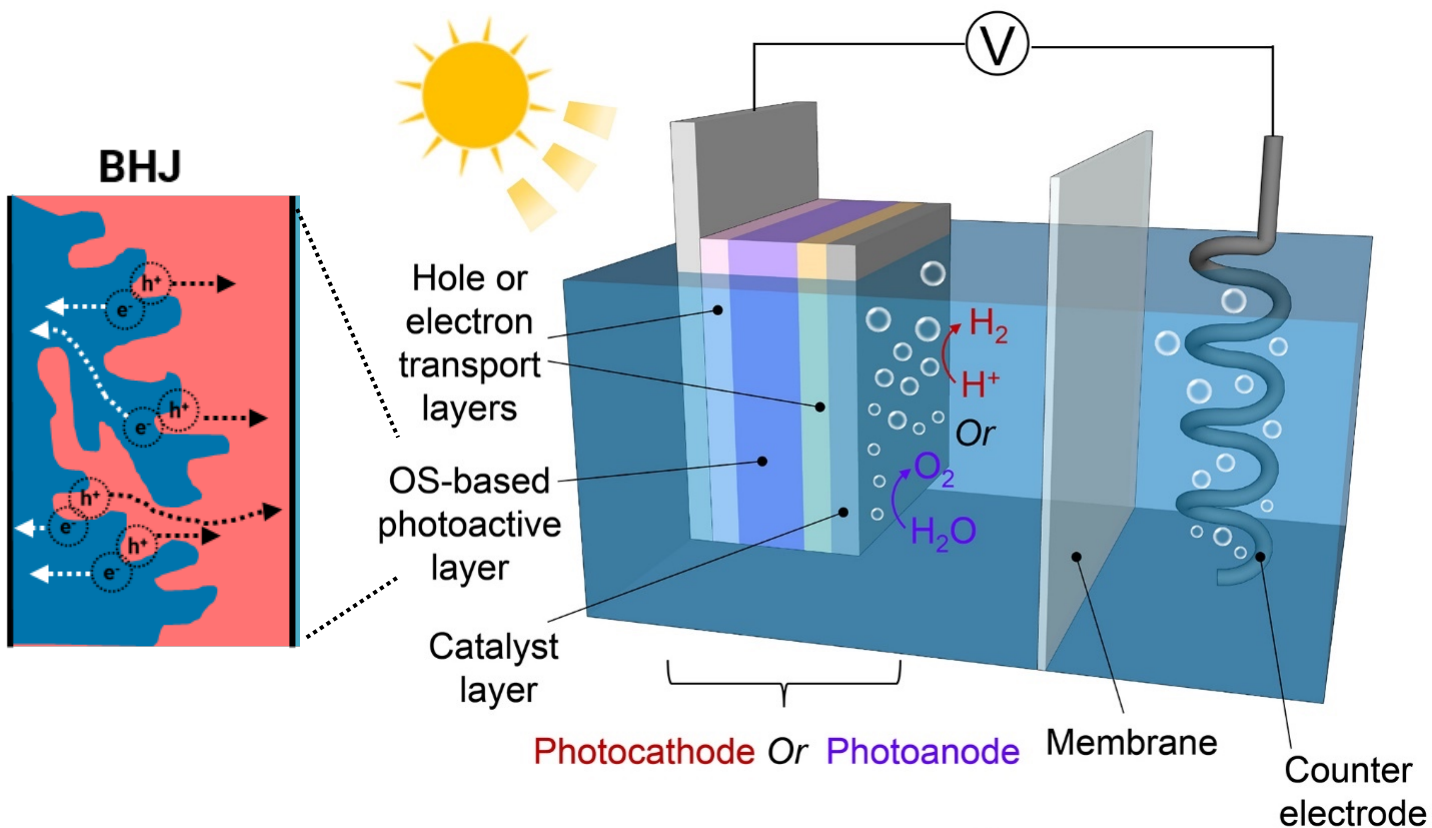


Organic semiconductors

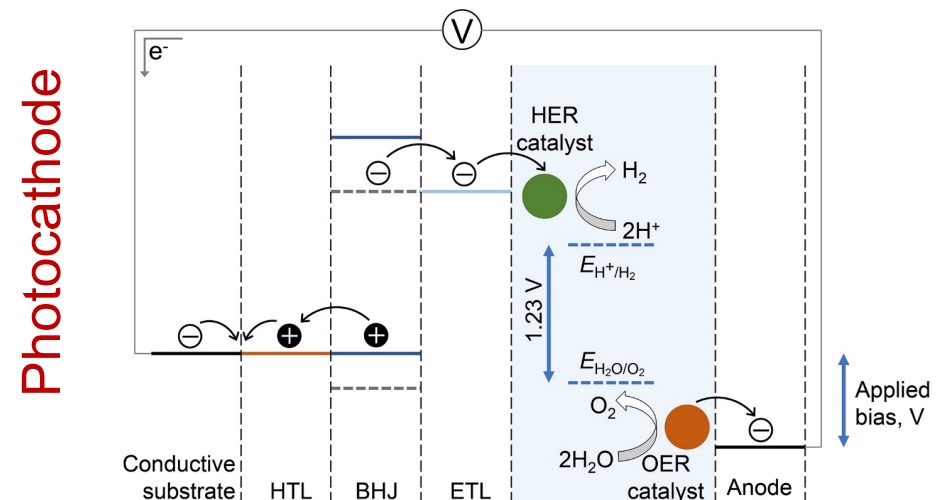
- ✓ Tunable energy levels
- ✓ Solution-processing & low temperature processing



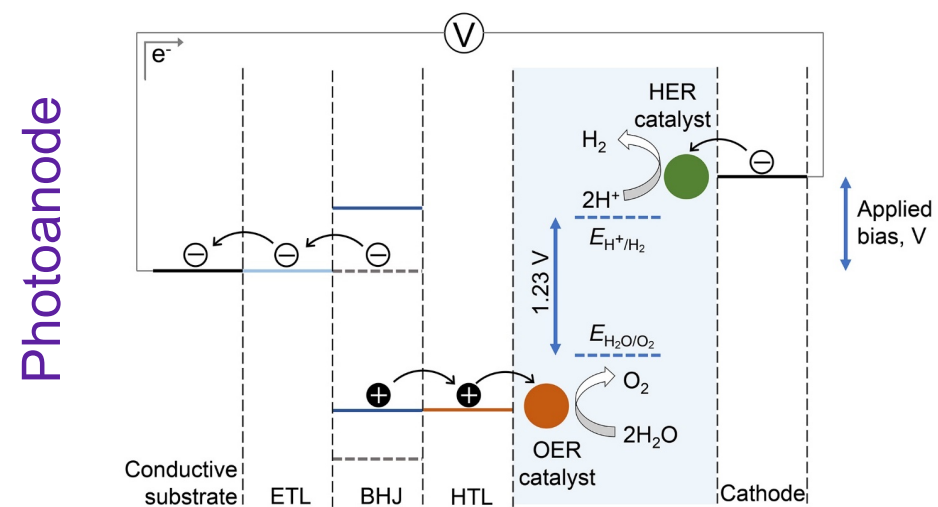
Solar-to-fuel conversion: "Artificial photosynthesis"



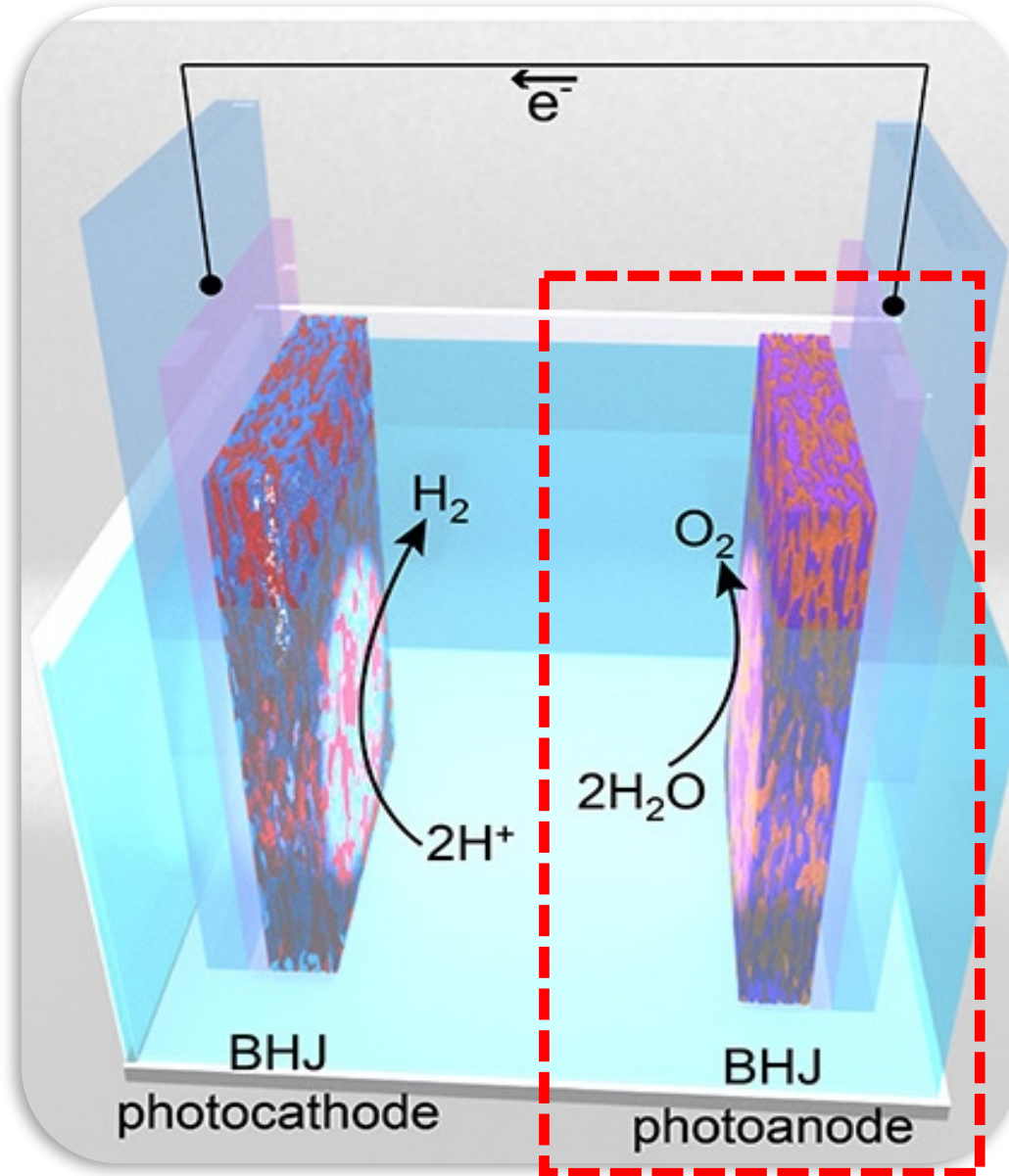
See review article: Yao et al. *Adv. Energy Mater.*, **2018**, *8*, 1802585.

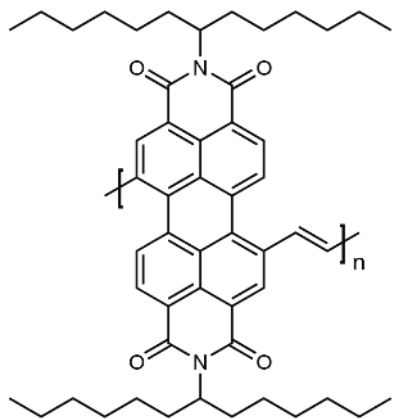


LUMO level of Acceptor higher than H^+/H_2 potential

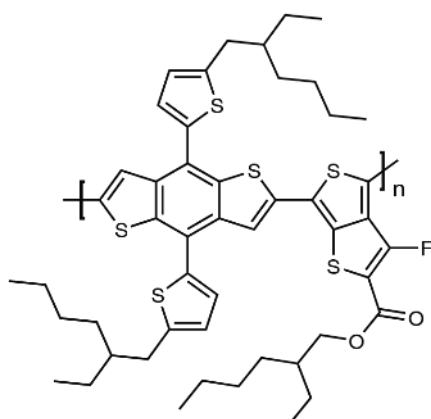


HOMO level of Donor lower than O_2/H_2O potential

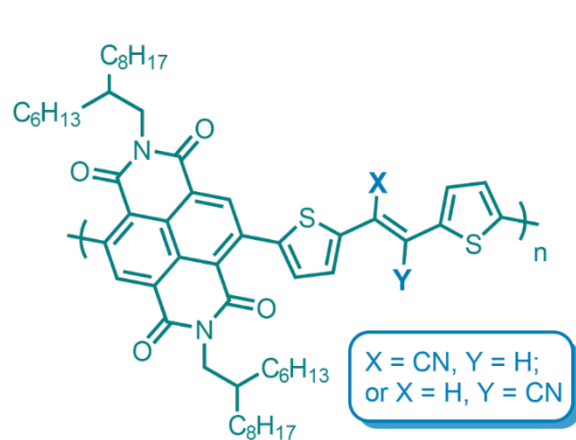
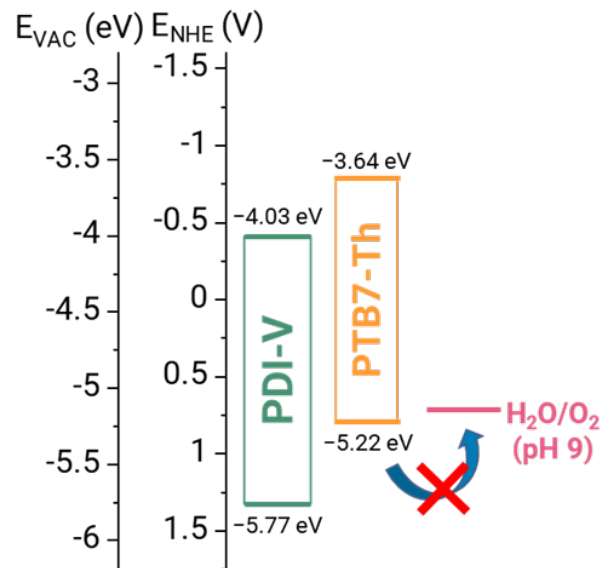




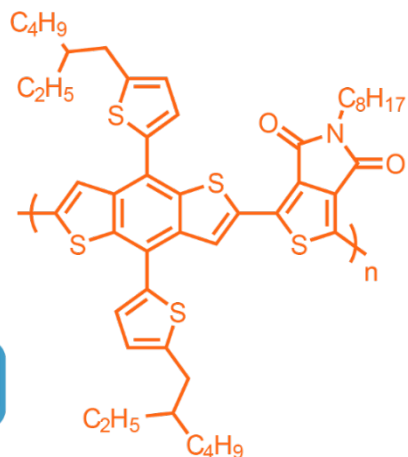
PDI-V (acceptor)



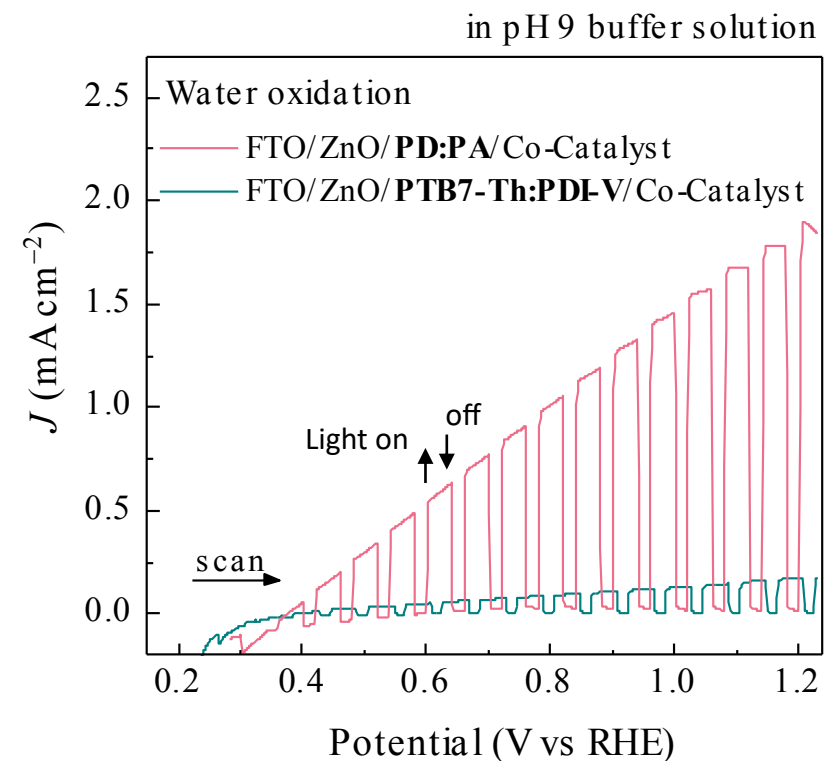
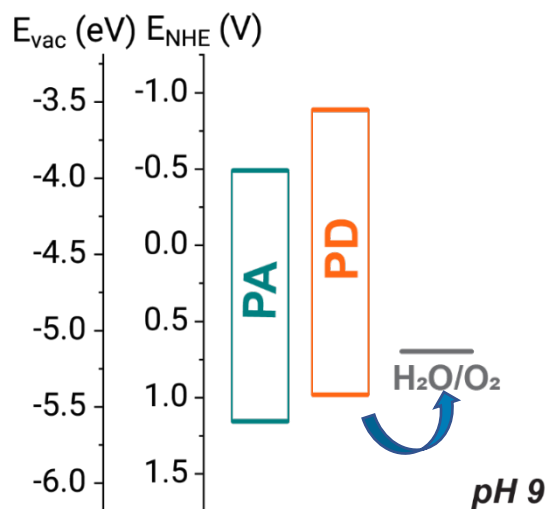
PTB7-Th (donor)

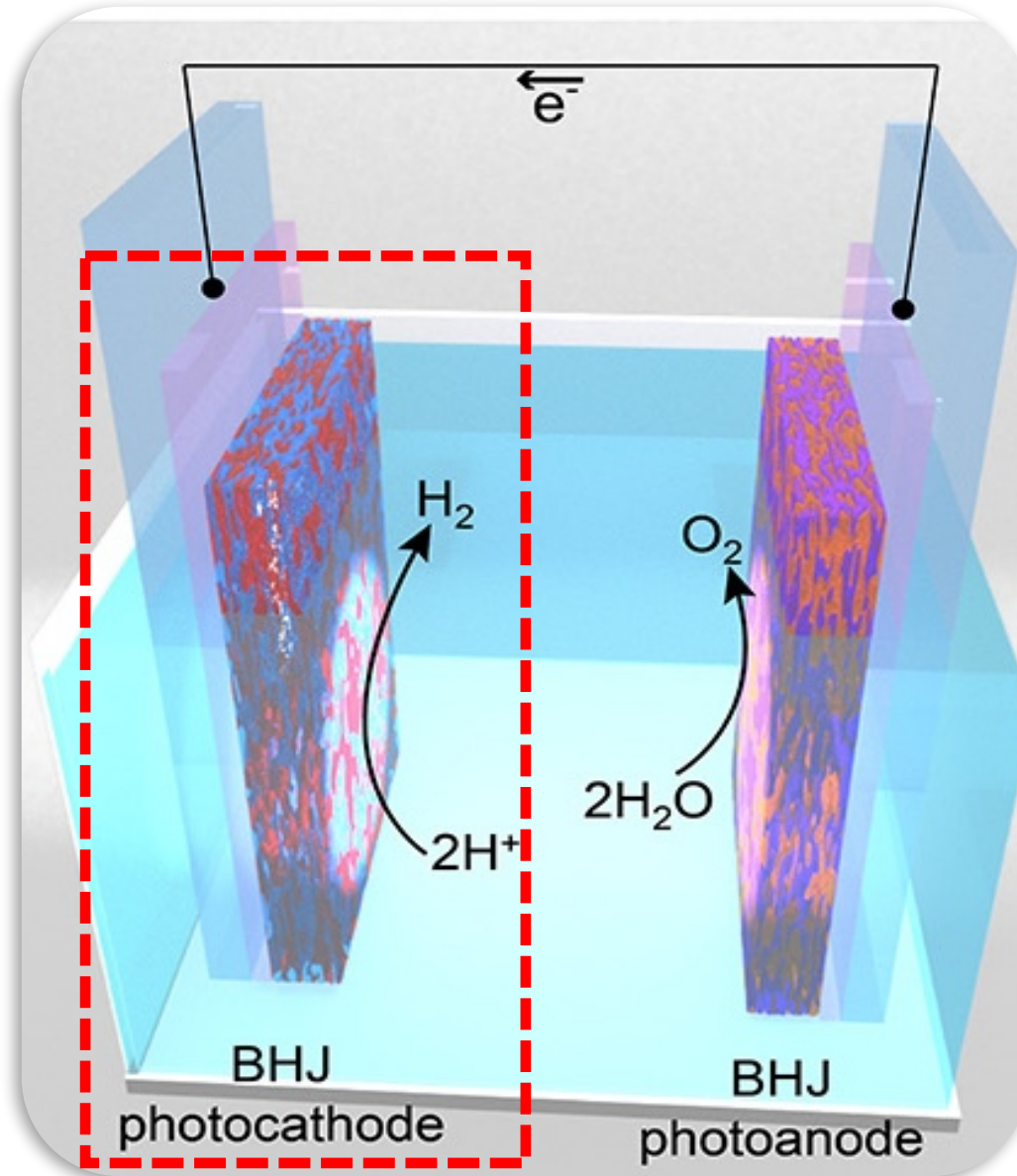


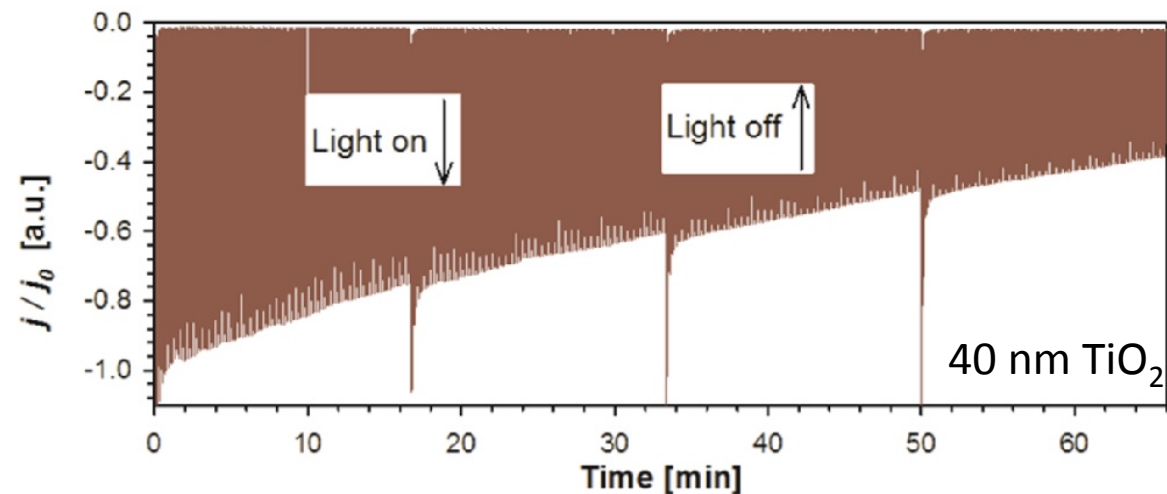
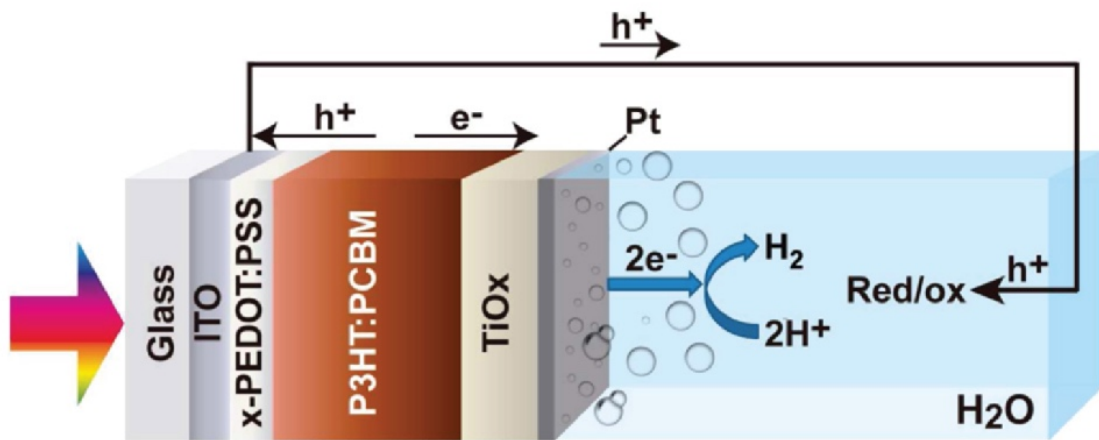
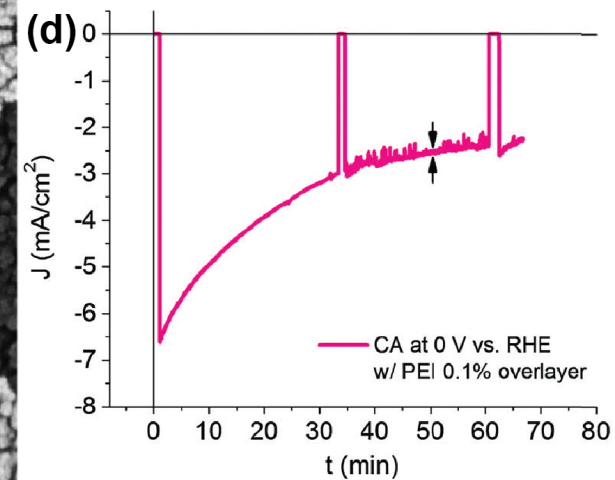
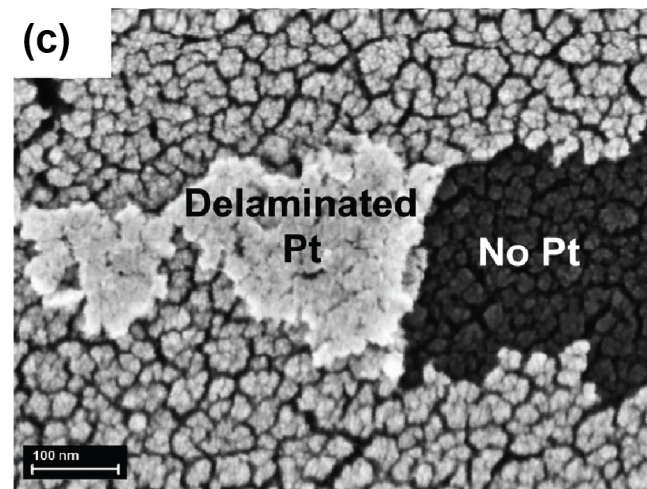
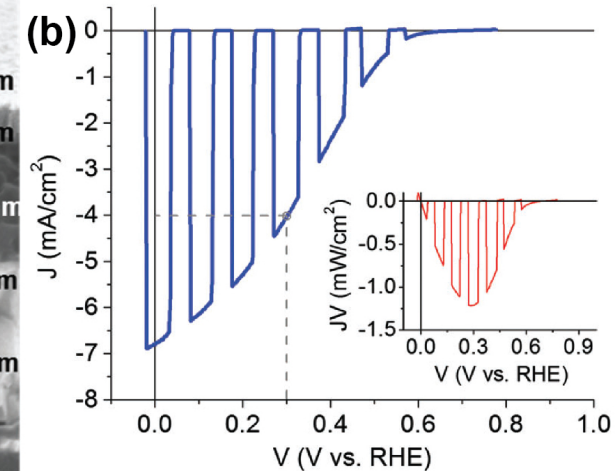
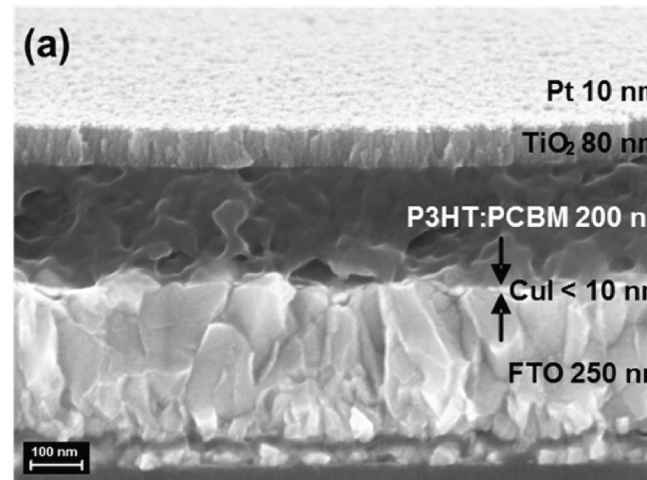
PNDITCVT (PA)



PBDTTTPD (PD)

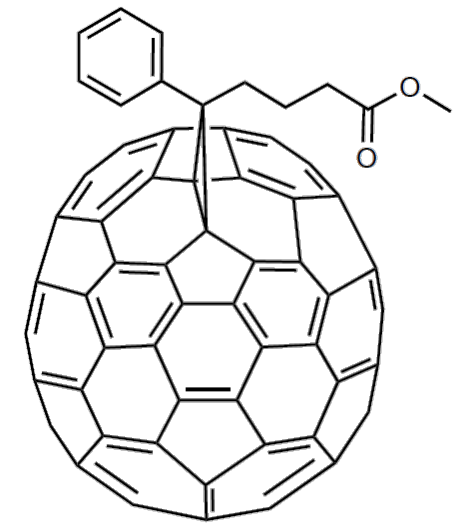
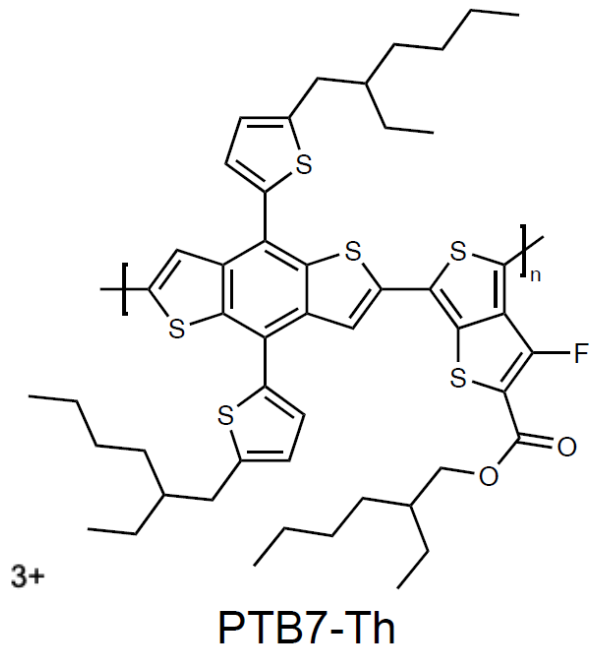
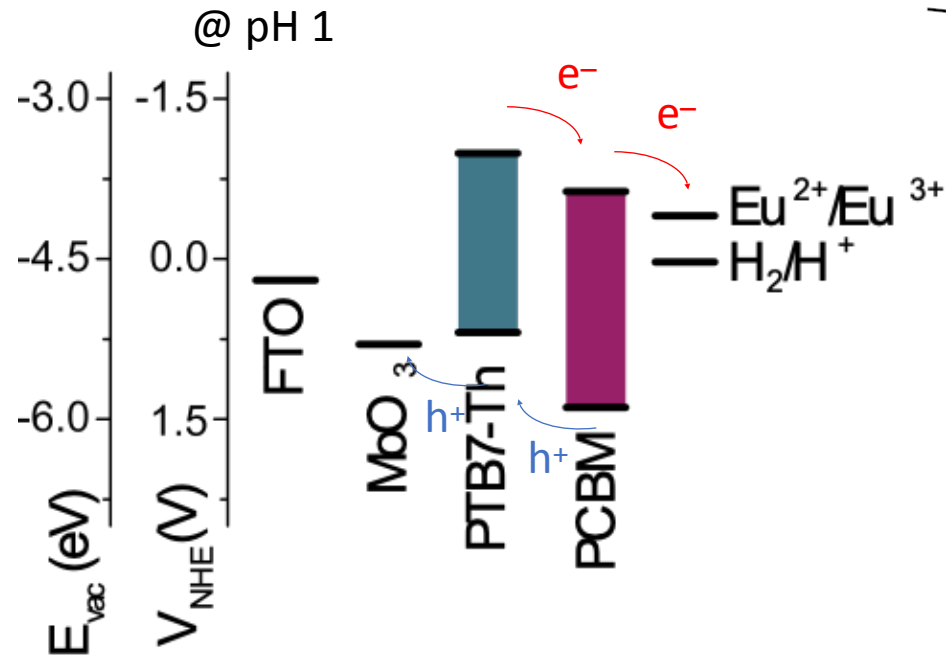
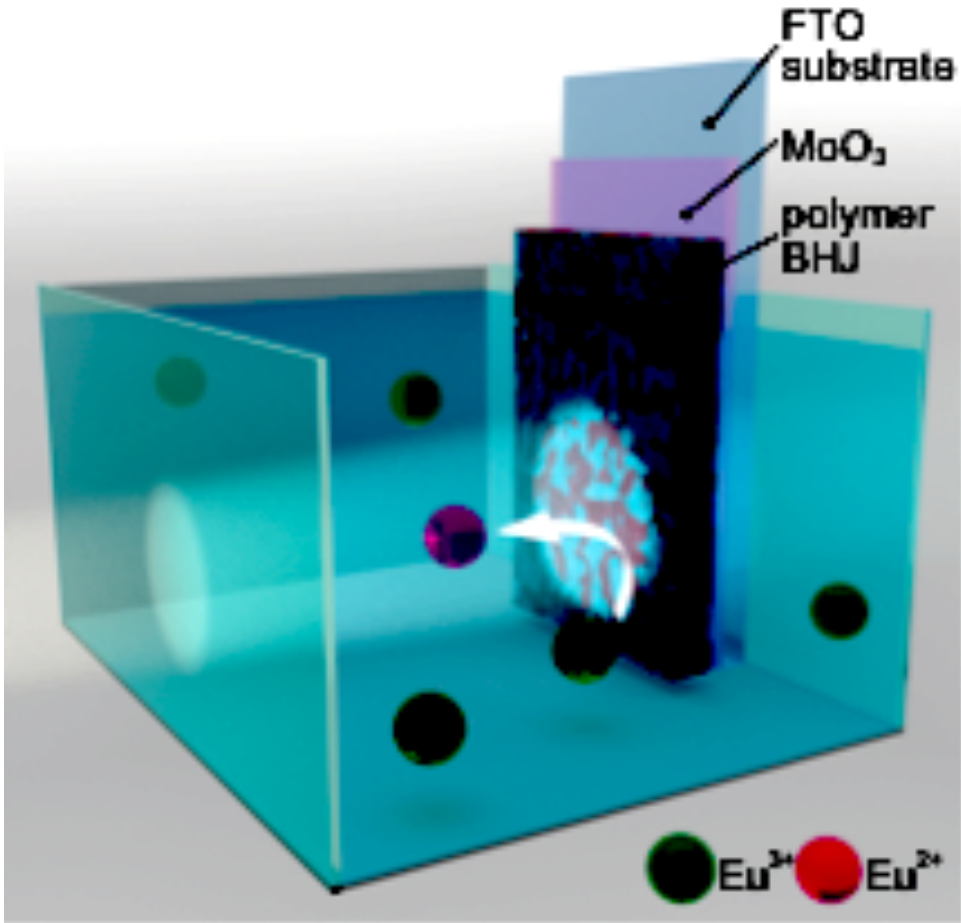




M. Haro et al., *J. Phys. Chem. C* **2015**, *119*, 6488.H. Comas Rojas et al., *Energy & Environmental Science* **2016**, *9*, 3710.

EPFL Why is a BHJ in Water So Unstable?

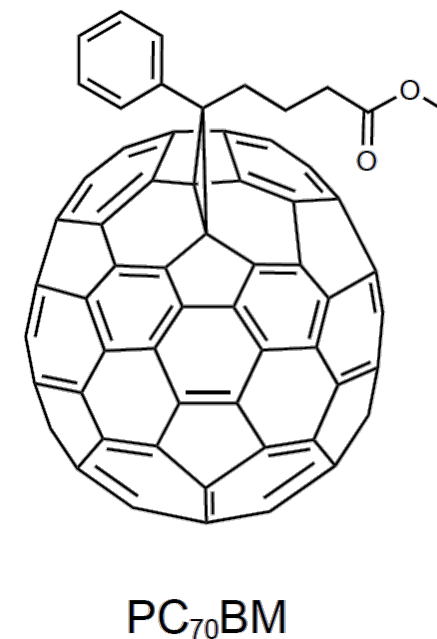
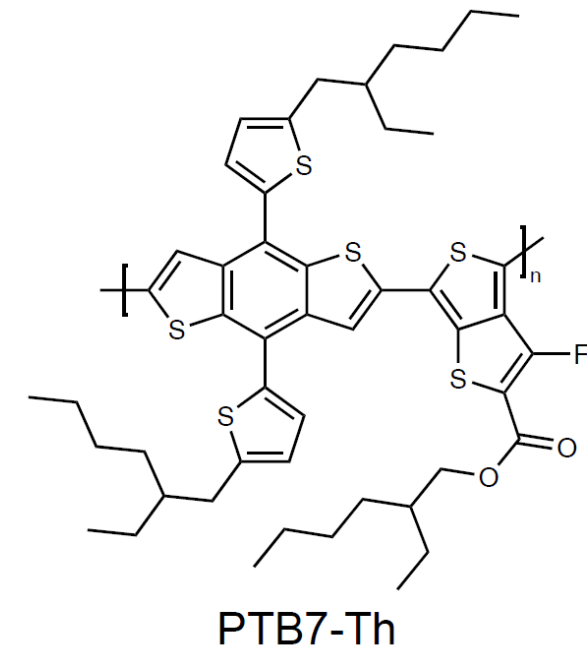
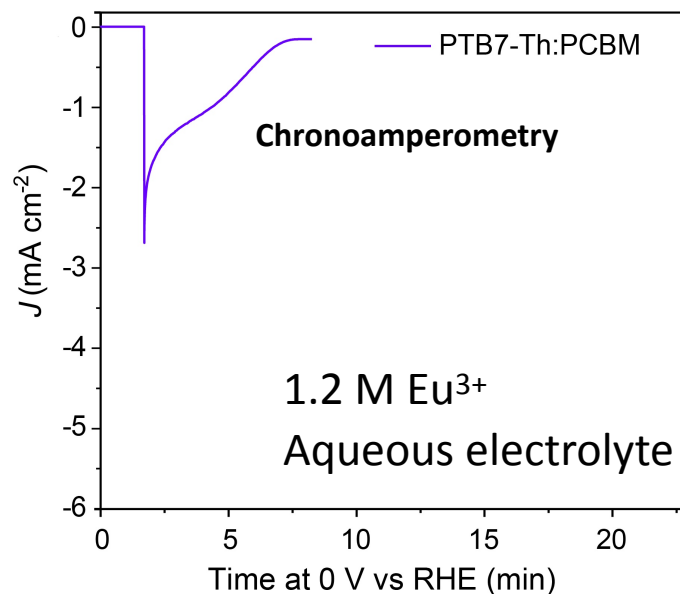
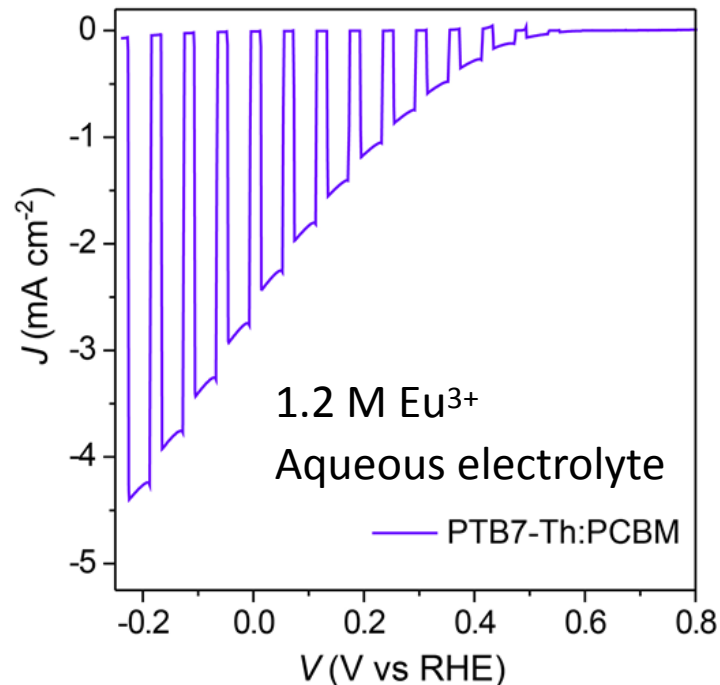
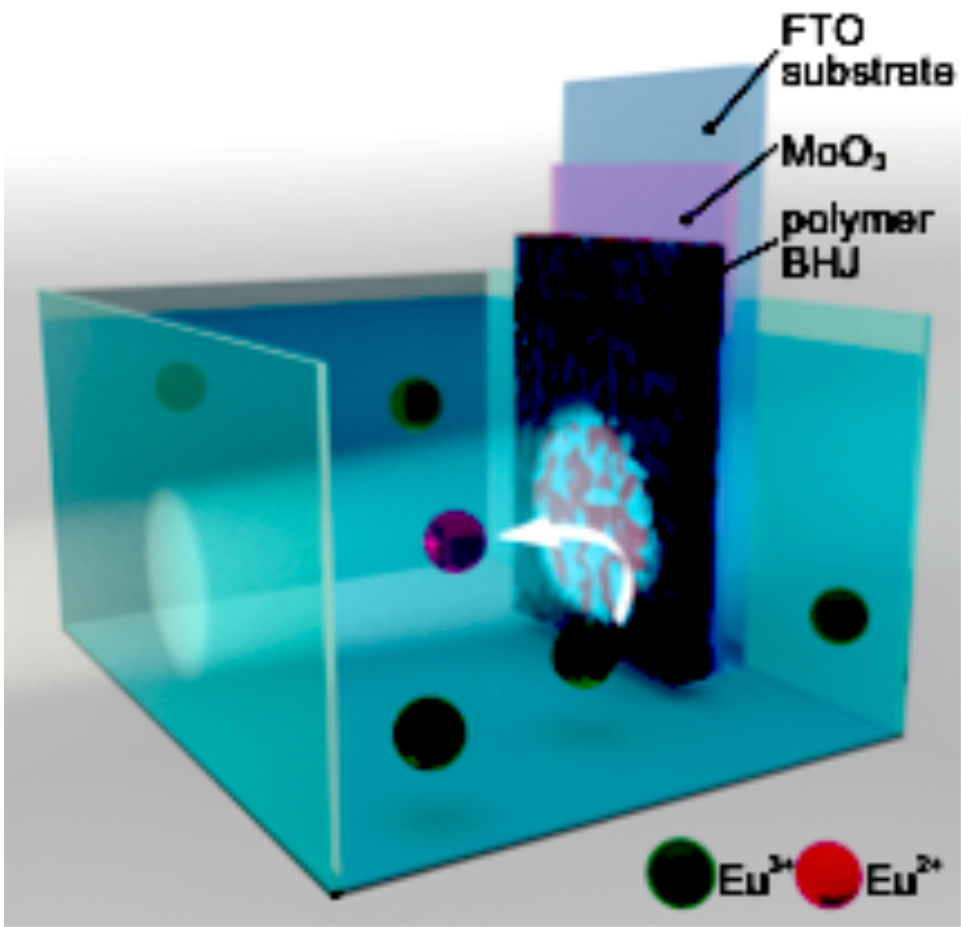
Or can a direct BHJ/water junction photocathode be stable?



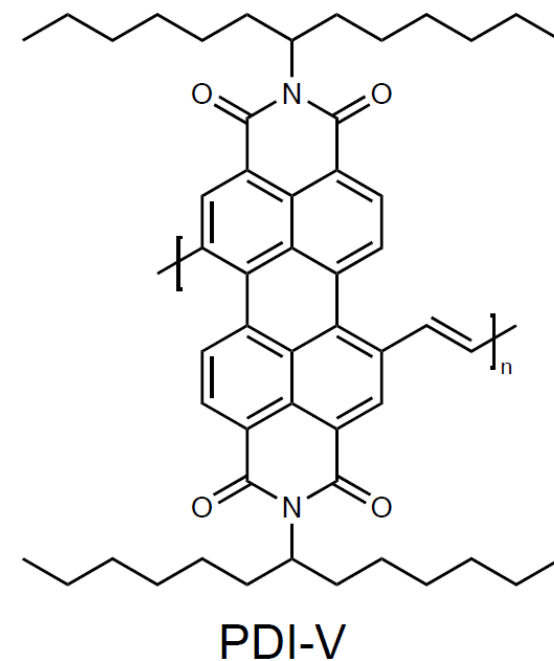
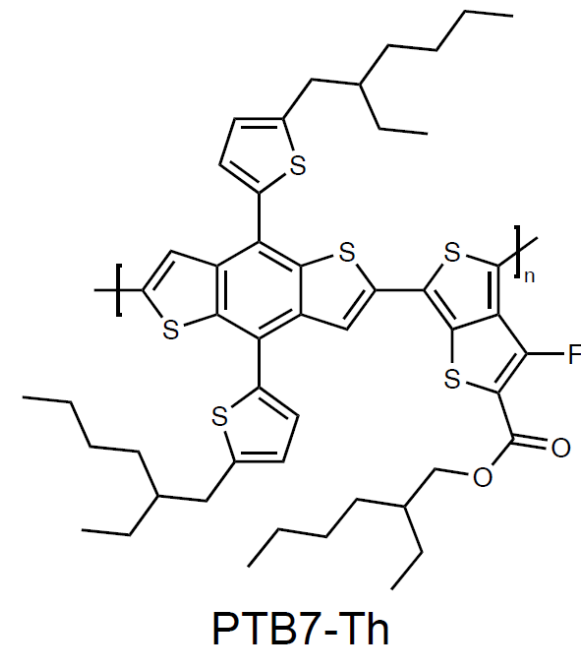
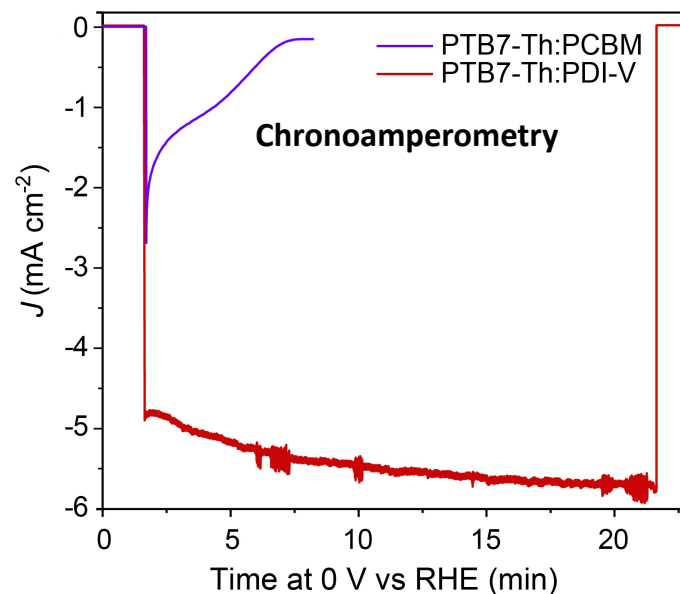
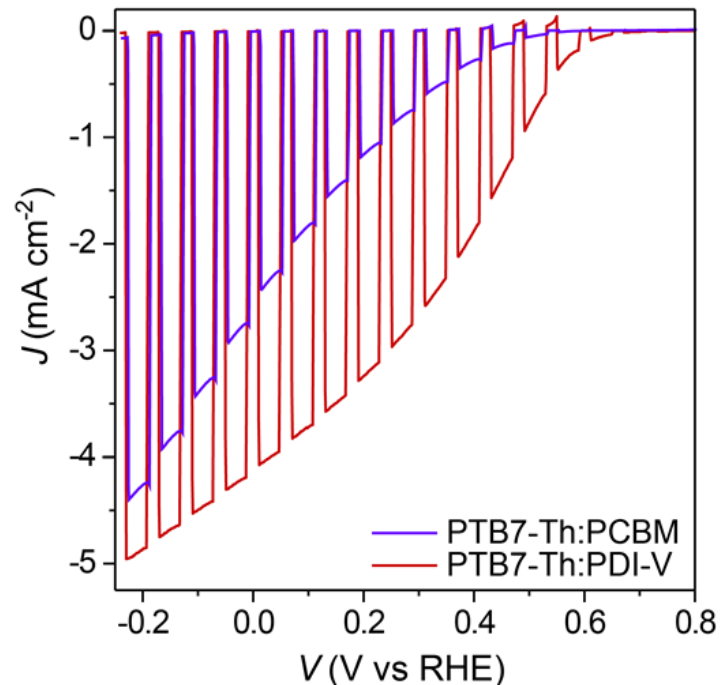
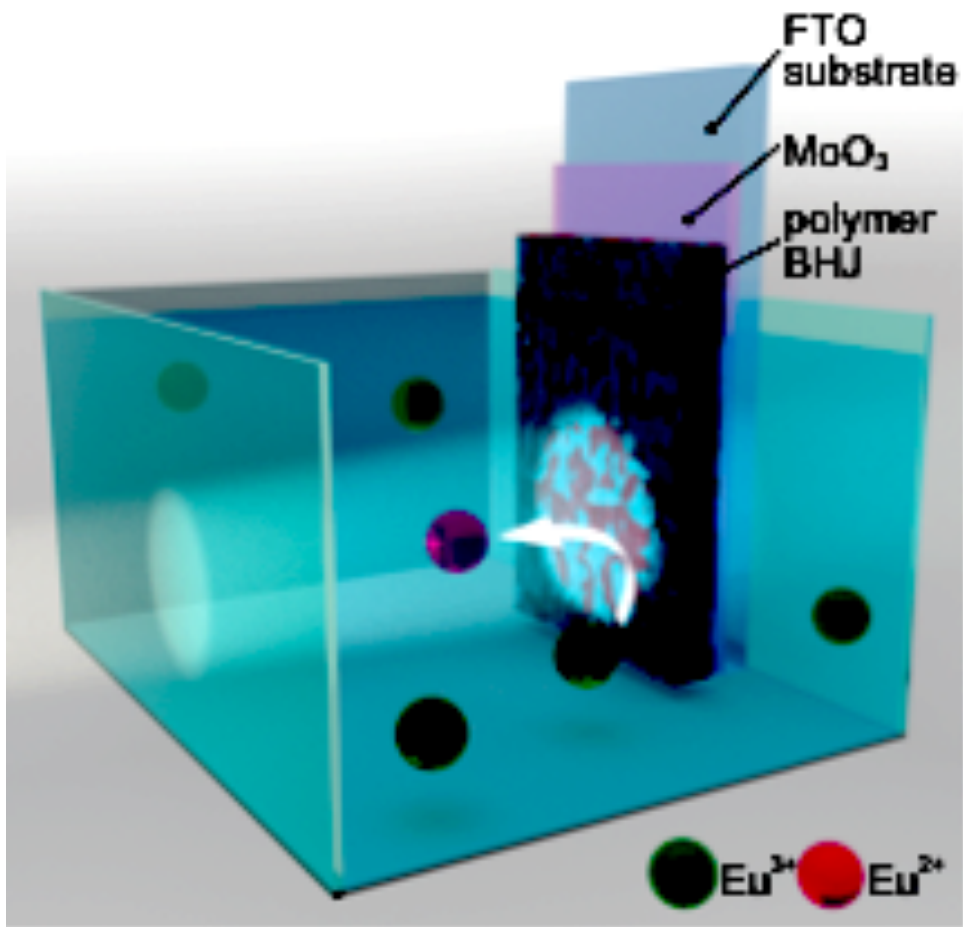
Study with sacrificial electrolyte (carrier scavenger that easily oxidised or reduced)

EPFL Why is a BHJ in Water So Unstable?

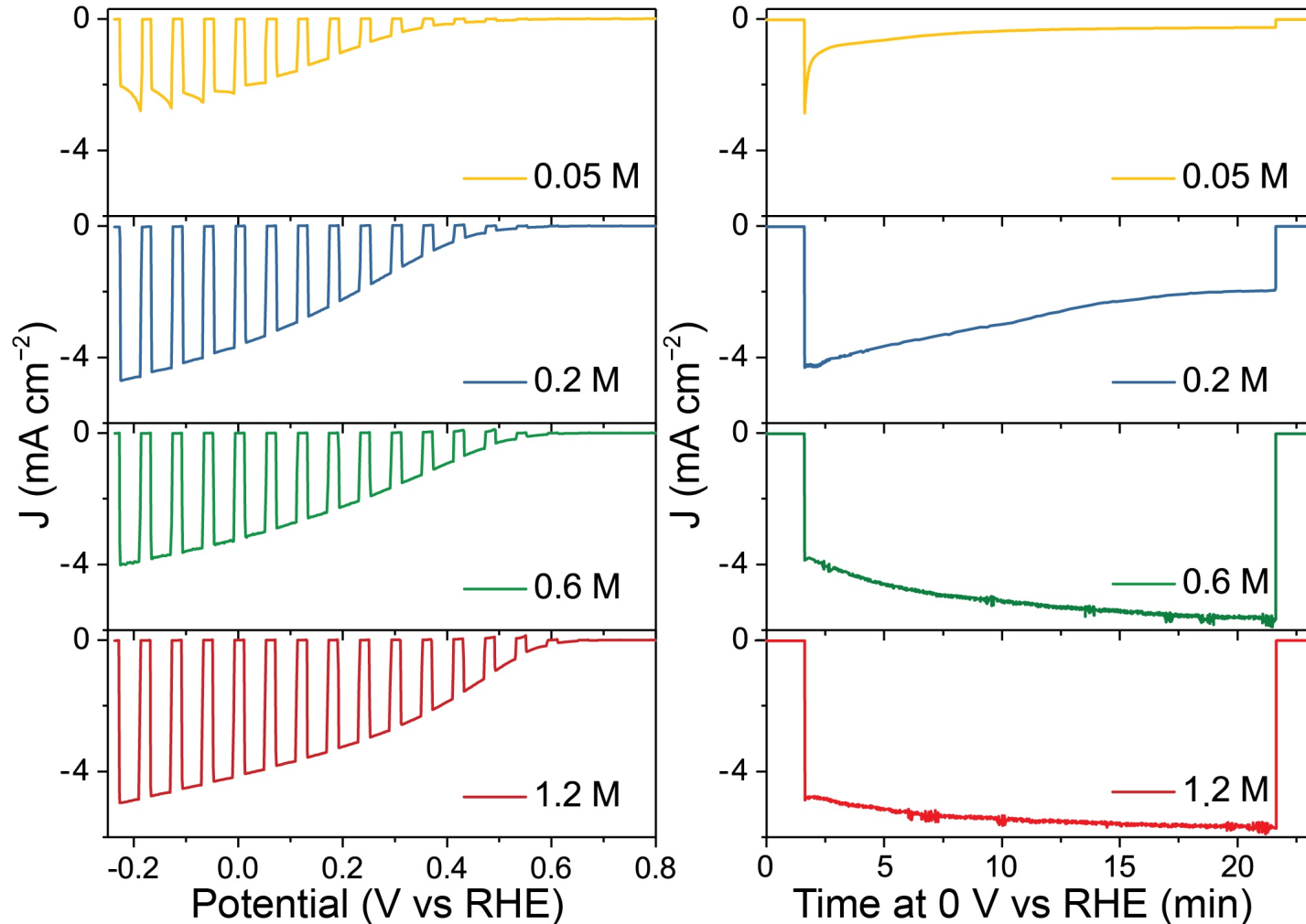
Or can a direct BHJ/water junction photocathode be stable?



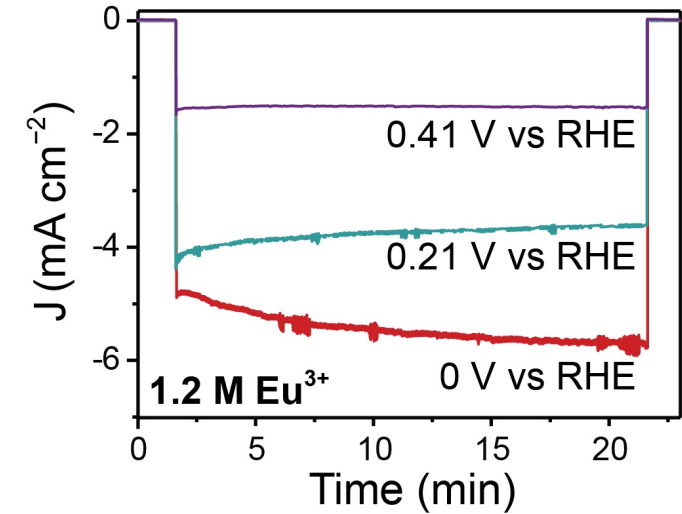
Or can a direct BHJ/water junction photocathode be stable?



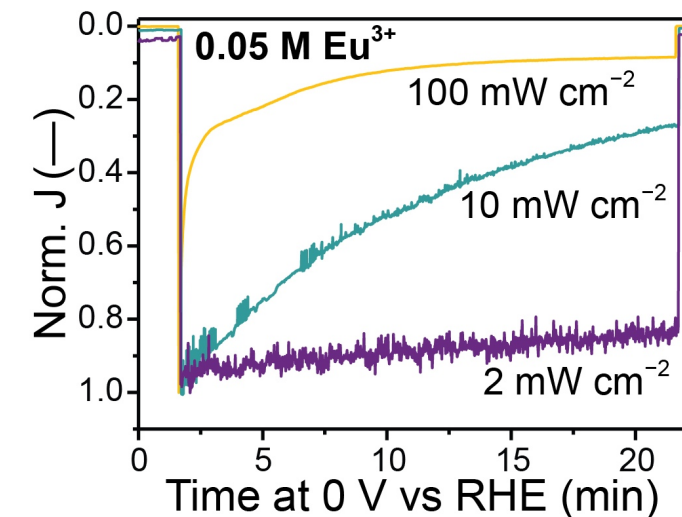
Changing the Eu^{3+} concentration:



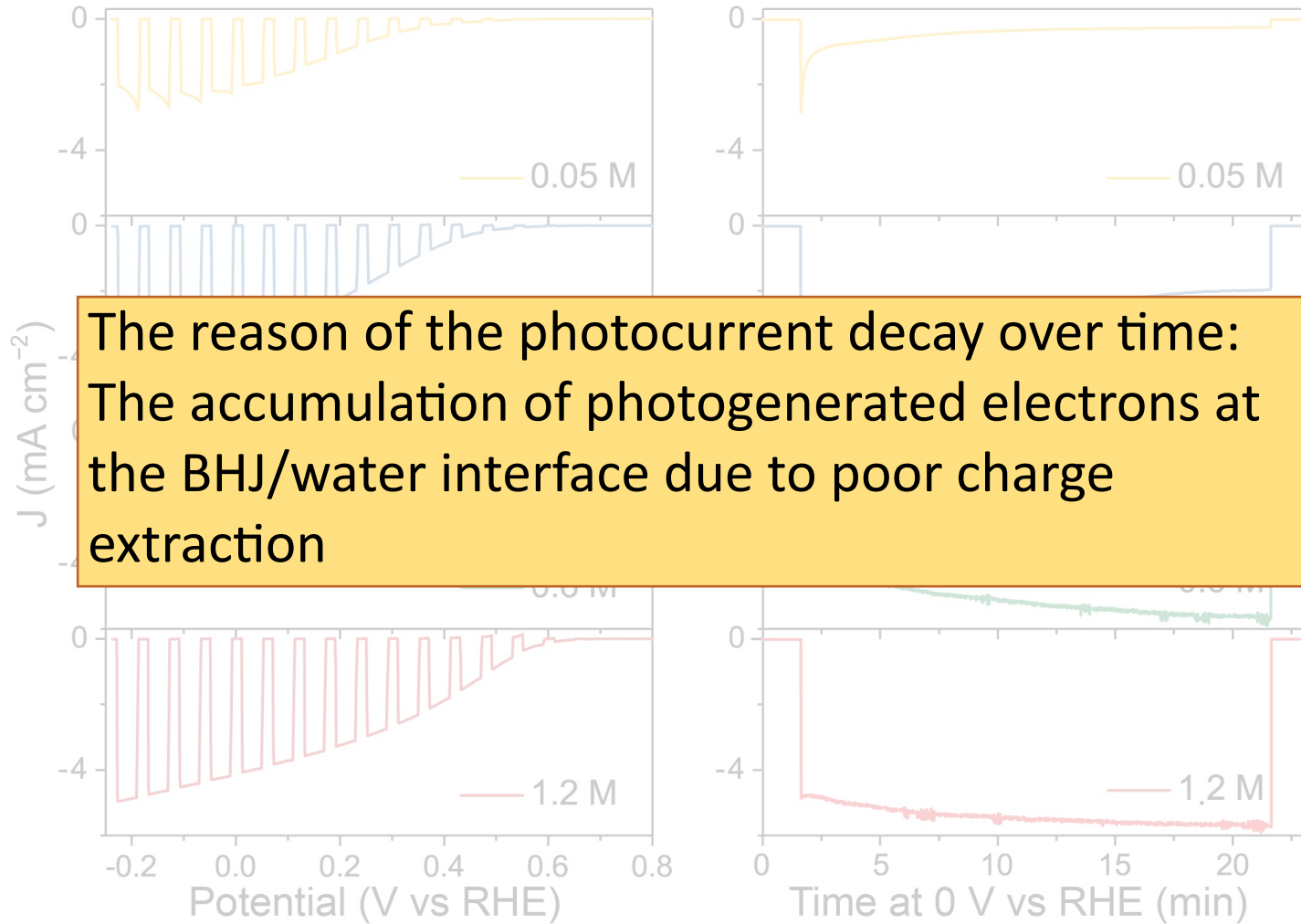
Changing the applied potential:



Changing the illumination intensity:

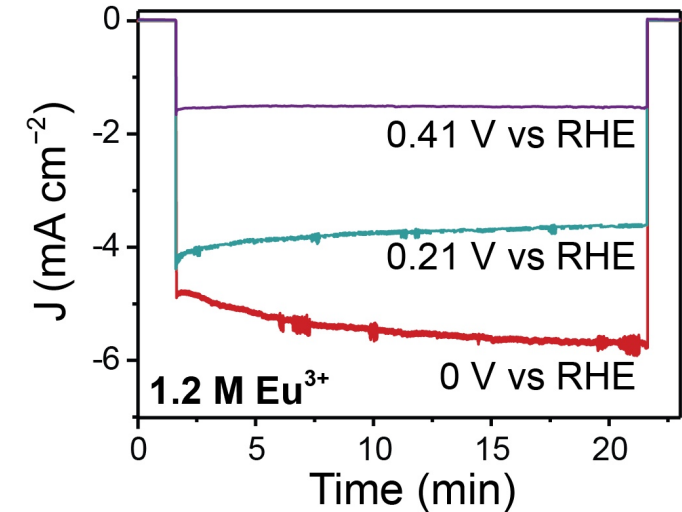


Changing the Eu^{3+} concentration:

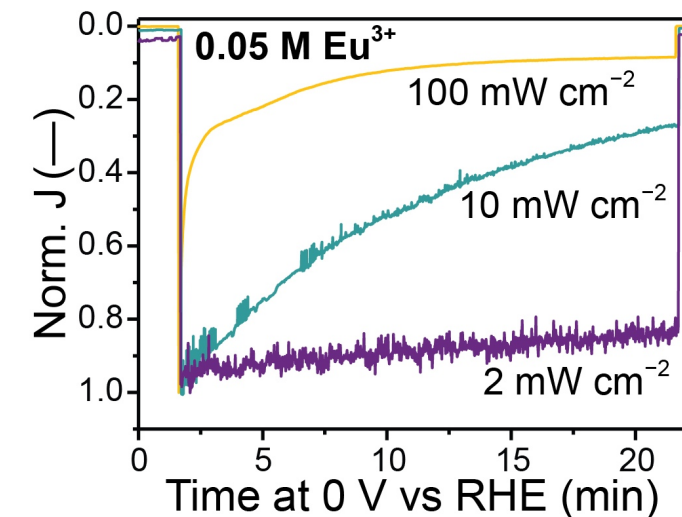


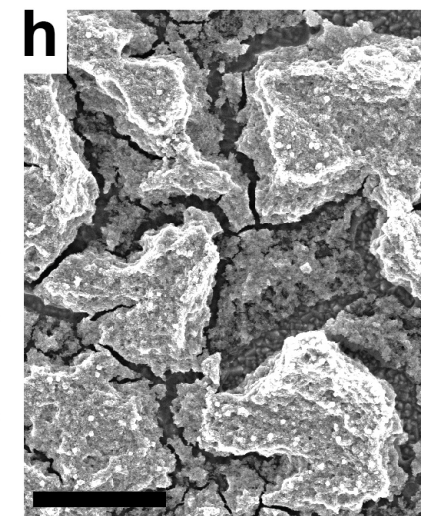
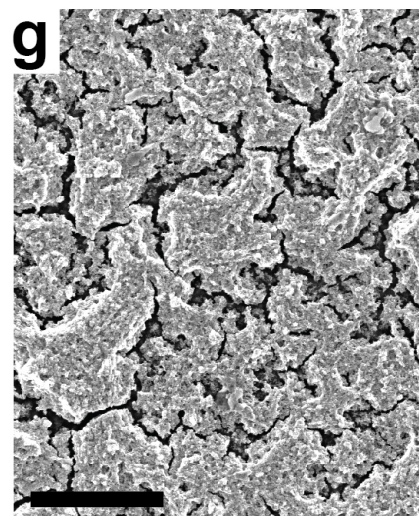
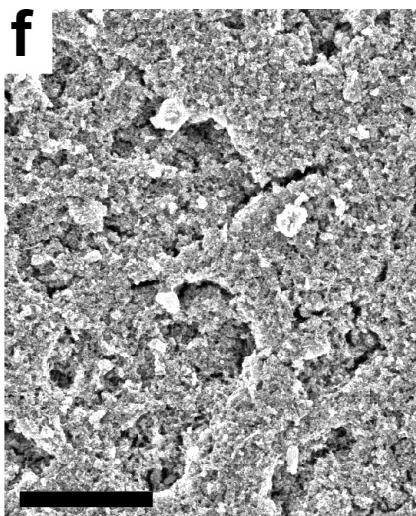
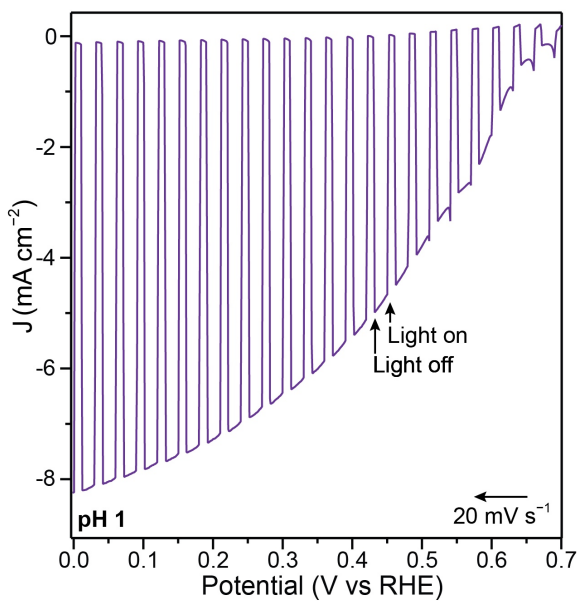
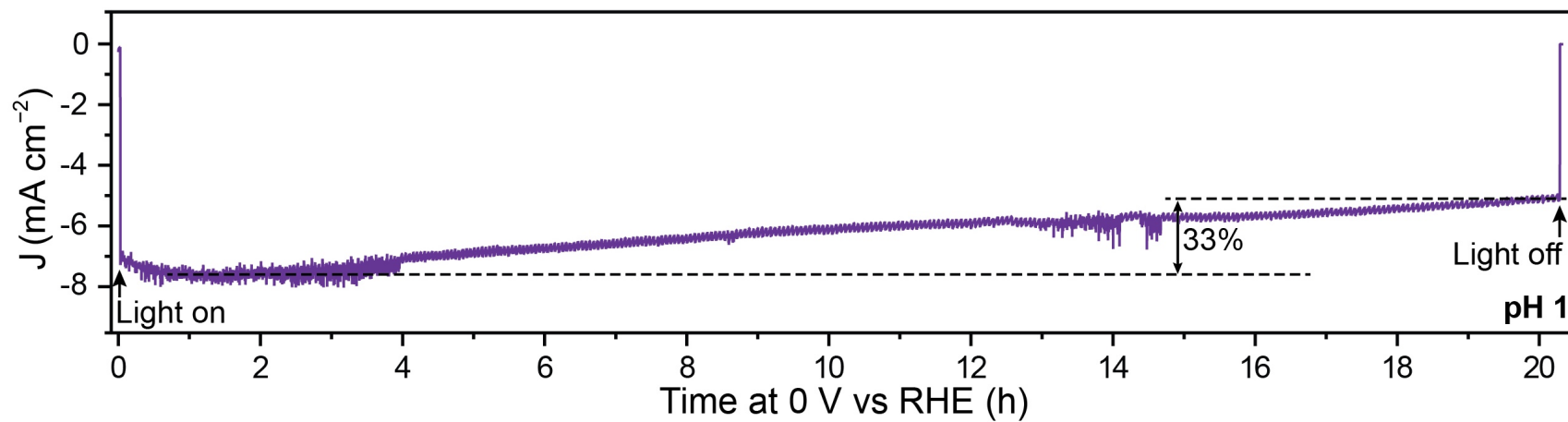
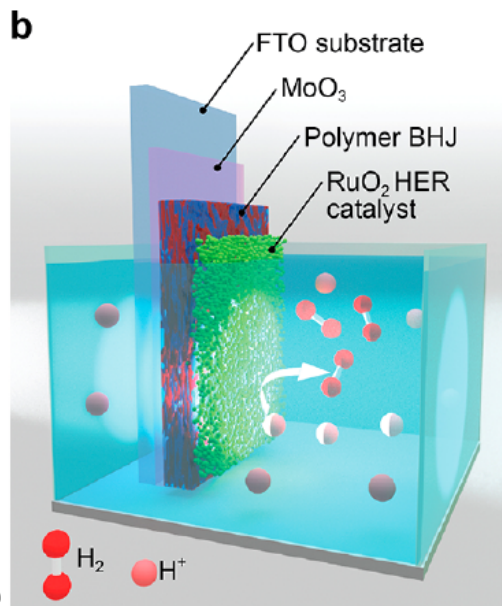
The reason of the photocurrent decay over time:
The accumulation of photogenerated electrons at the BHJ/water interface due to poor charge extraction

Changing the applied potential:

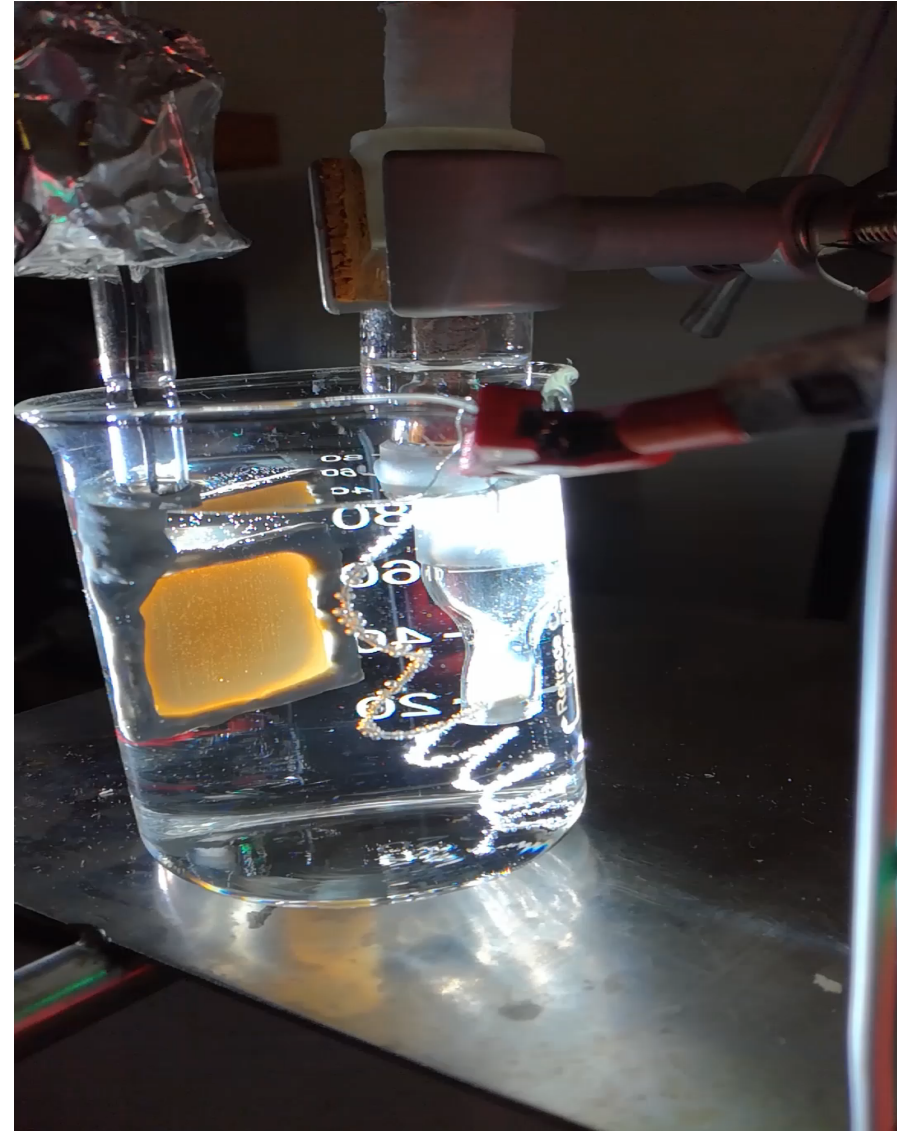
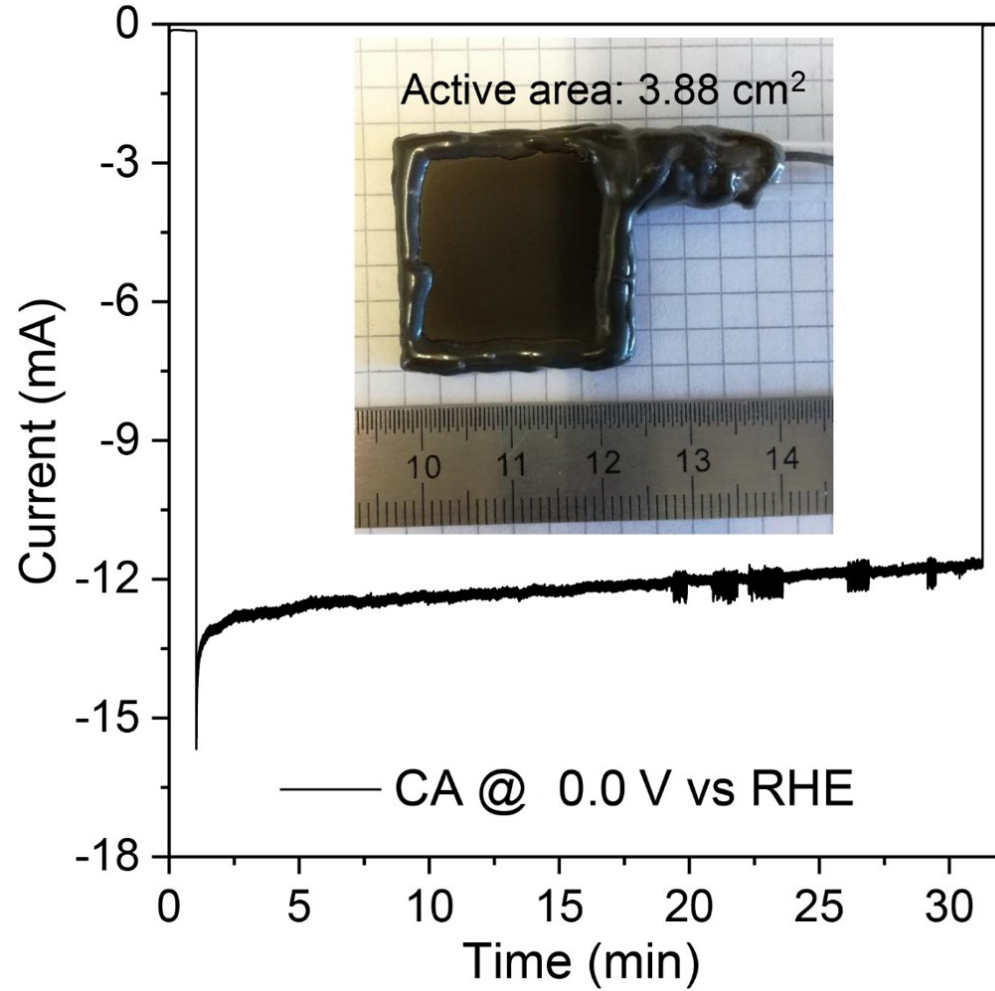


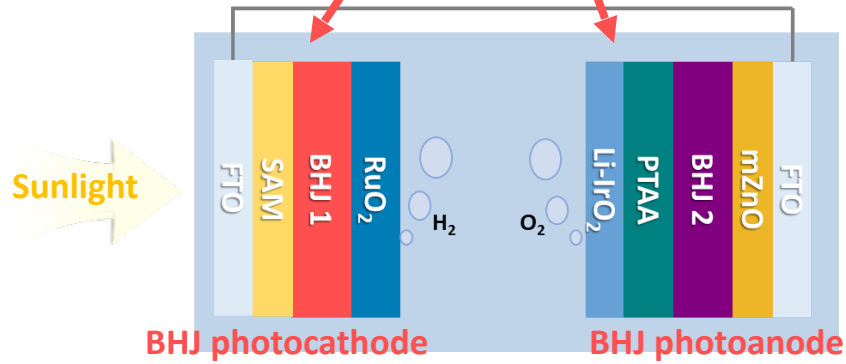
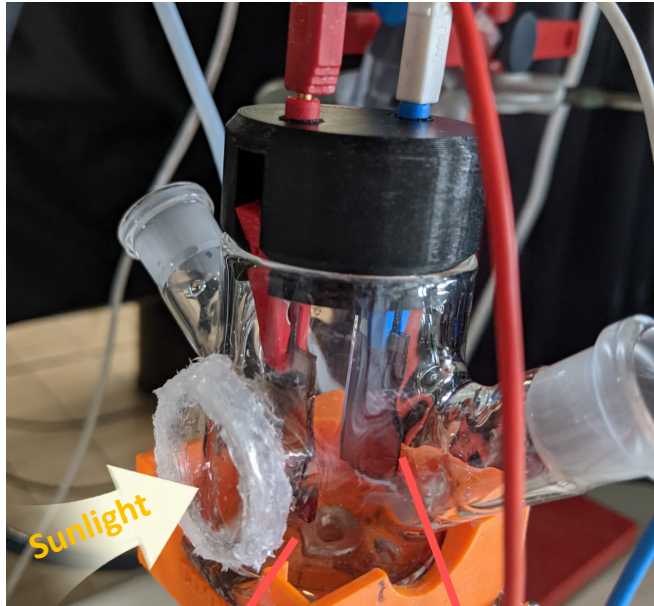
Changing the illumination intensity:





Scale bar: 1 μ m

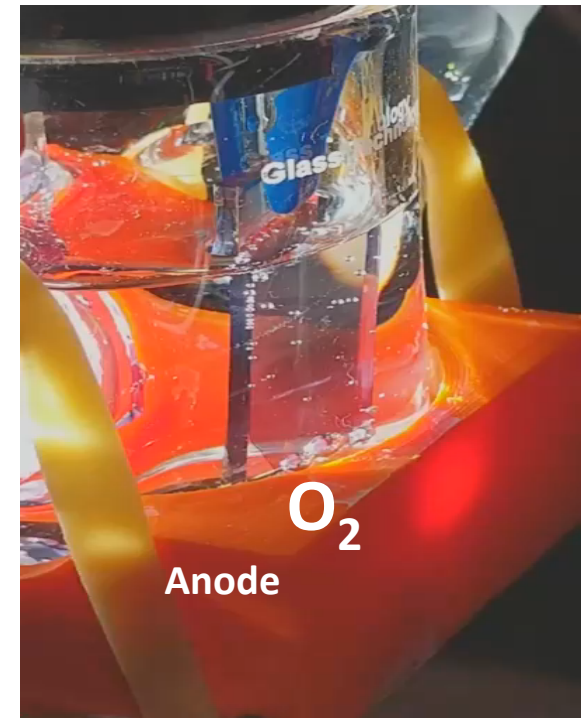
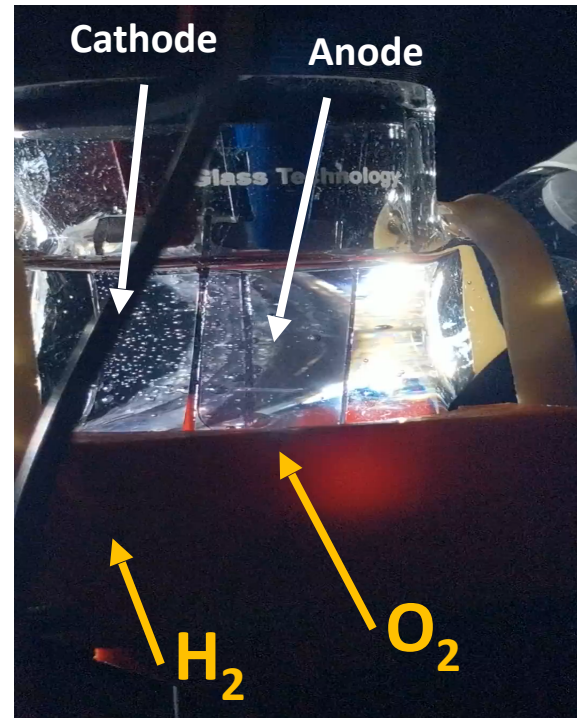




Complete solar water splitting at zero-bias
Without any capsulation or passivation

[Back]

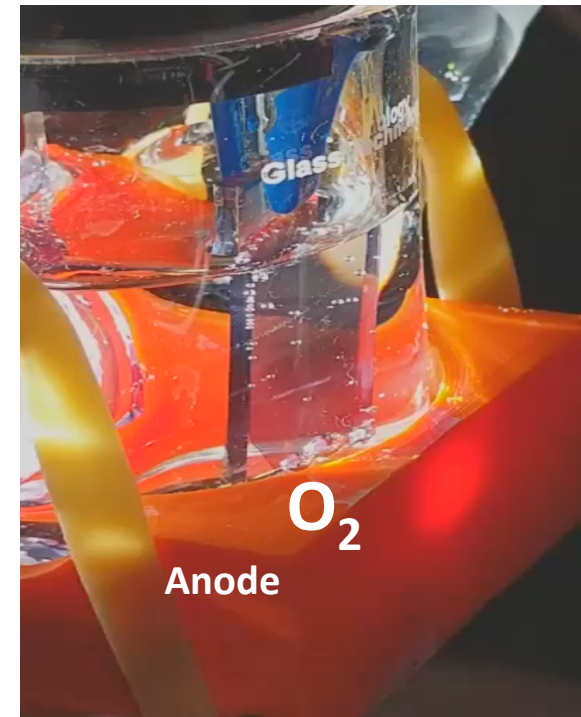
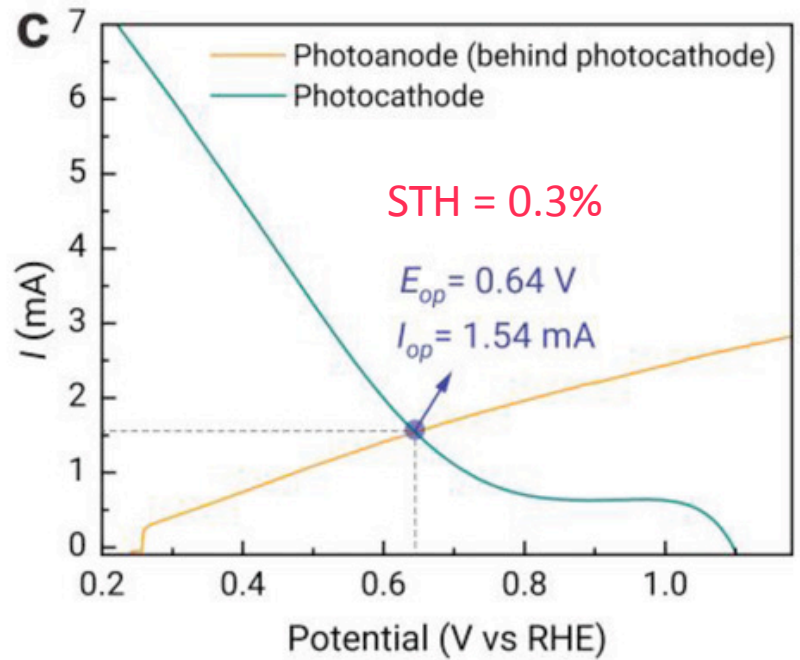
[Side]



Complete solar water splitting at zero-bias Without any capsulation or passivation

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[Side]



D. Zhang, et al., Adv. Energy Mater., 2022, 2202363.